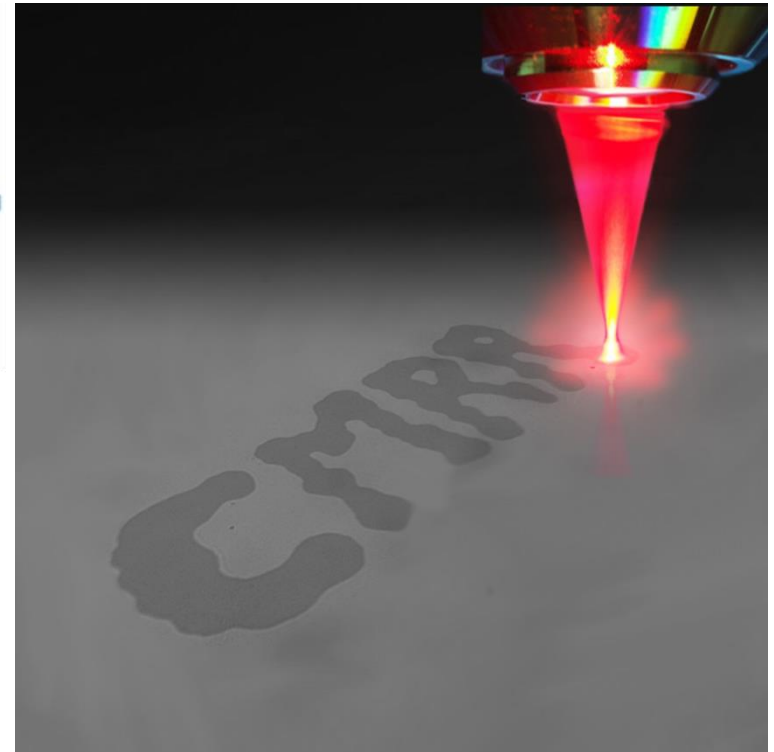
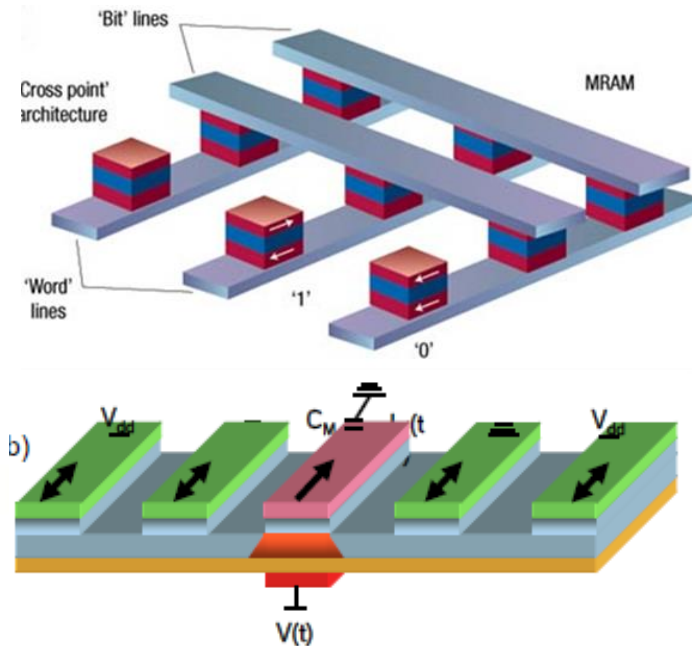


Bits of the Future: Emergent Physics for Advanced Magnetic Information Technologies

Eric E. Fullerton

Center for Magnetic Recording Research
University of California, San Diego

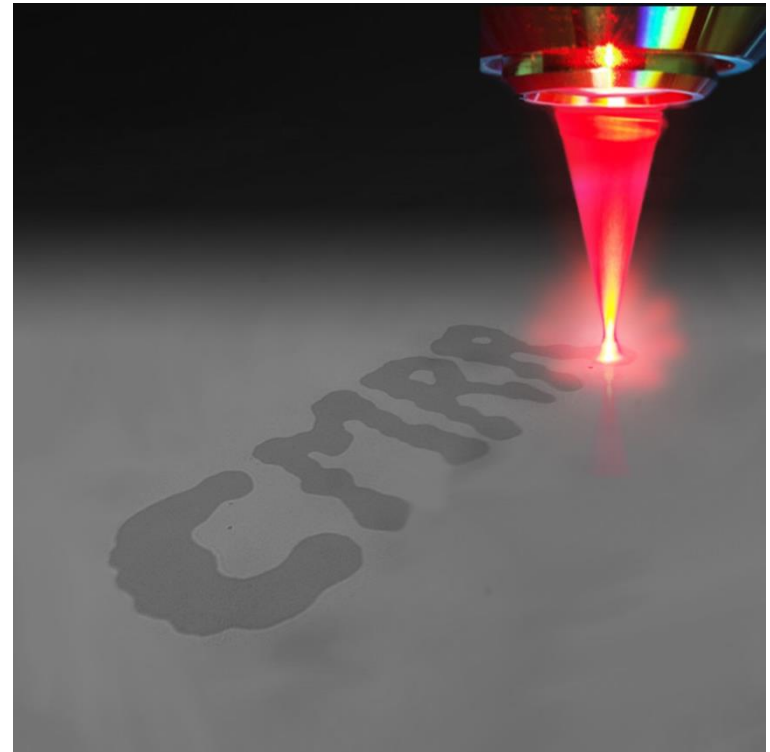


Bits of the Future: Emergent Physics for Advanced Magnetic Information Technologies

Eric E. Fullerton

Center for Magnetic Recording Research
University of California, San Diego

- A bit of history and introduction
- All-optical control / storage
- Current control / memory
- Conclusions and outlook



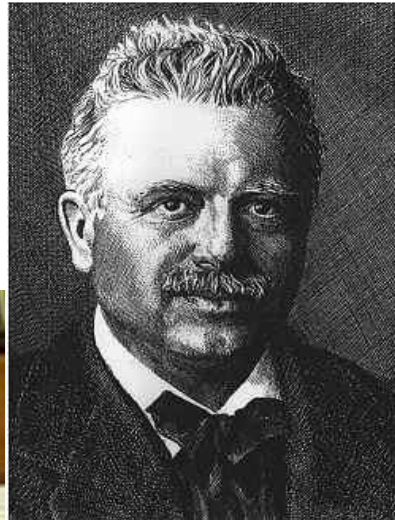
First magnetic recording 1898

Magnetic Recording Invented

Valdemar Poulsen

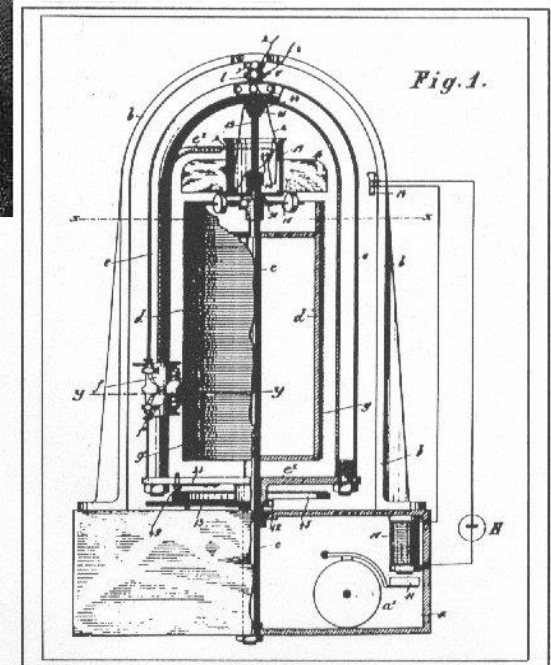


Valdemar Poulsen's wire recorder from 1898
(Danish technical museum www.tekniskmuseum.dk)



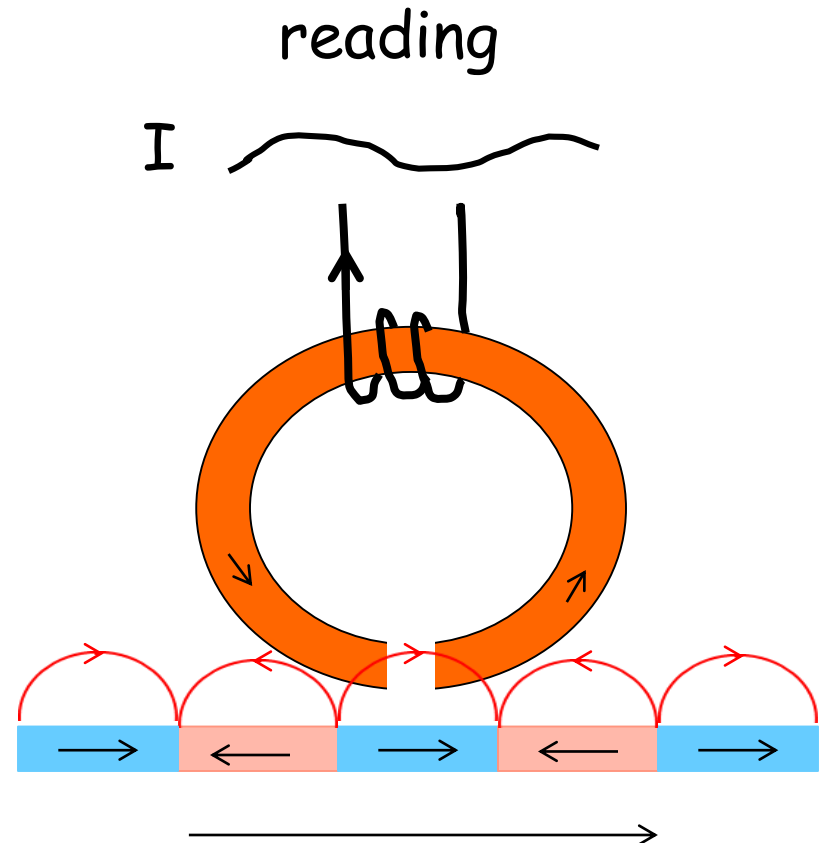
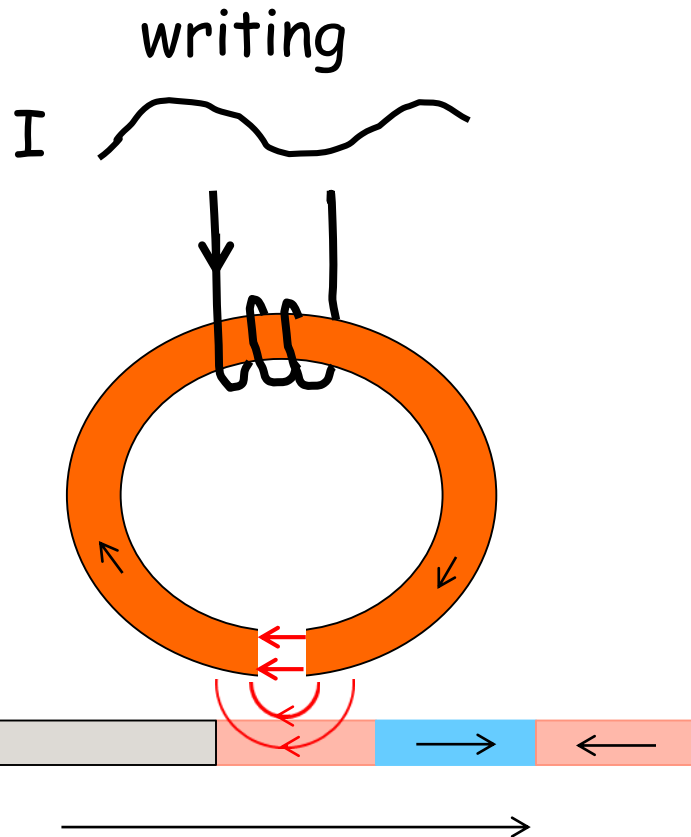
MAGNETIC RECORDING

Invented by Valdemar Poulsen
Copenhagen, Denmark 1898



"Method of Recording and
Reproducing Sounds or Signals."

Magnetic recording



Killer applications

patent : The invention is of great importance for telephonic purposes

phone communications can be received by the apparatus when the subscriber is absent, whereas upon his return he can cause the communications to be repeated by the apparatus.

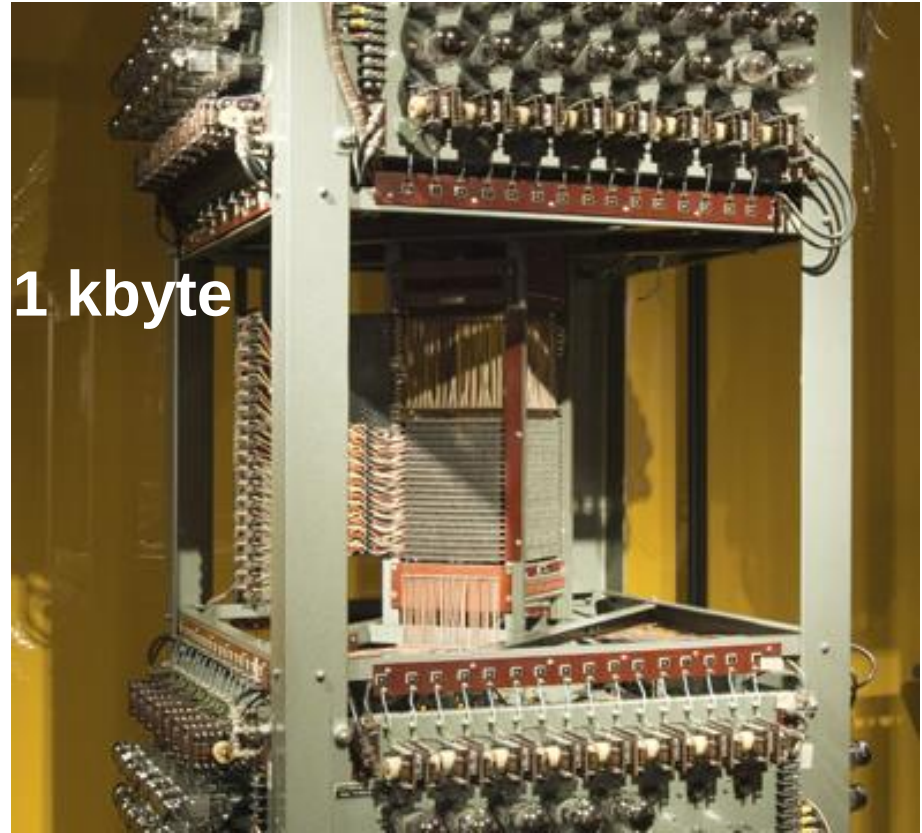
If, for example, the message, "The subscriber is not at home at present, but will return at four o'clock, at which time please ring again," is fixed to the steel wire

Digital magnetic storage/memory



5 Mbyte

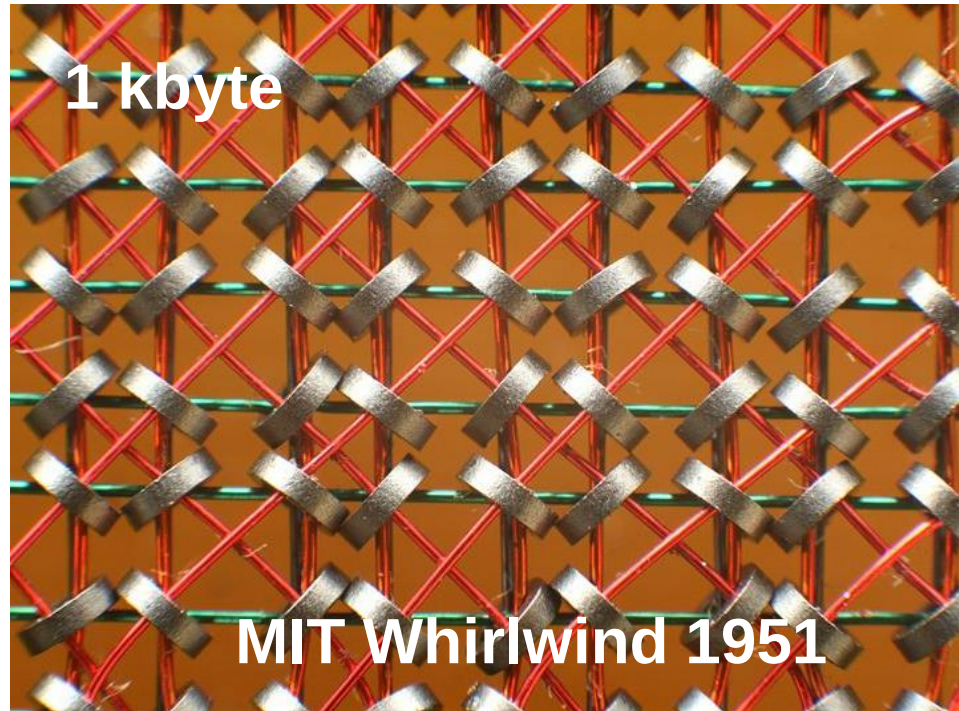
RAMAC 1956



1 kbyte

MIT Whirlwind 1951

Digital magnetic storage/memory



2 kbits/in²
70 kbits/s
50x 24 in dia disks
\$10,000,000/Gbyte

Cell Size: 1 mm²
Access time: 10 microseconds
Destructive read
Cost: \$1/bit

Current storage/memory

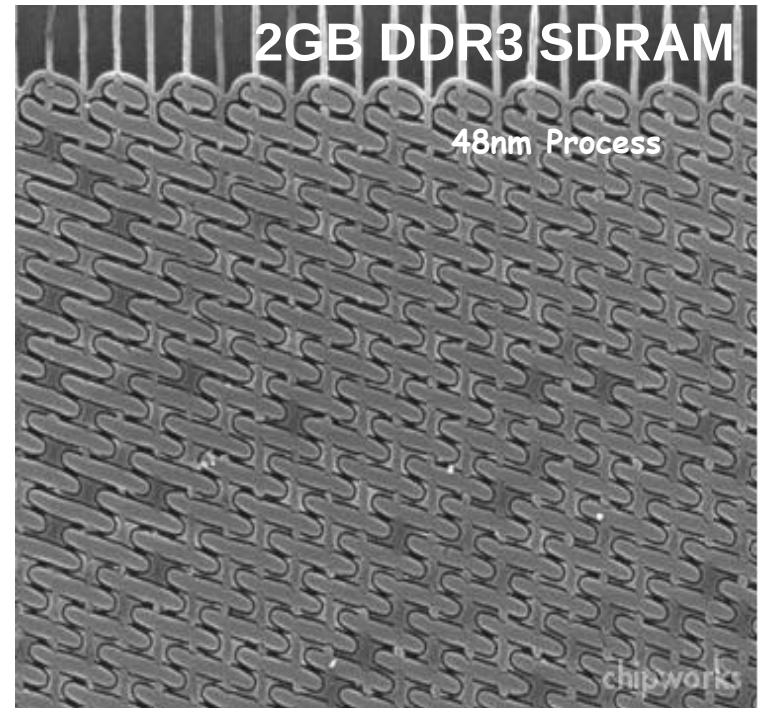
500 Gbyte mobile drive

1 x 2.5"
glass disk



630 Gbits/in² (3×10^8)
1.4 Gbits/s (2×10^4)
Non-volatile
\$0.15/Gbyte

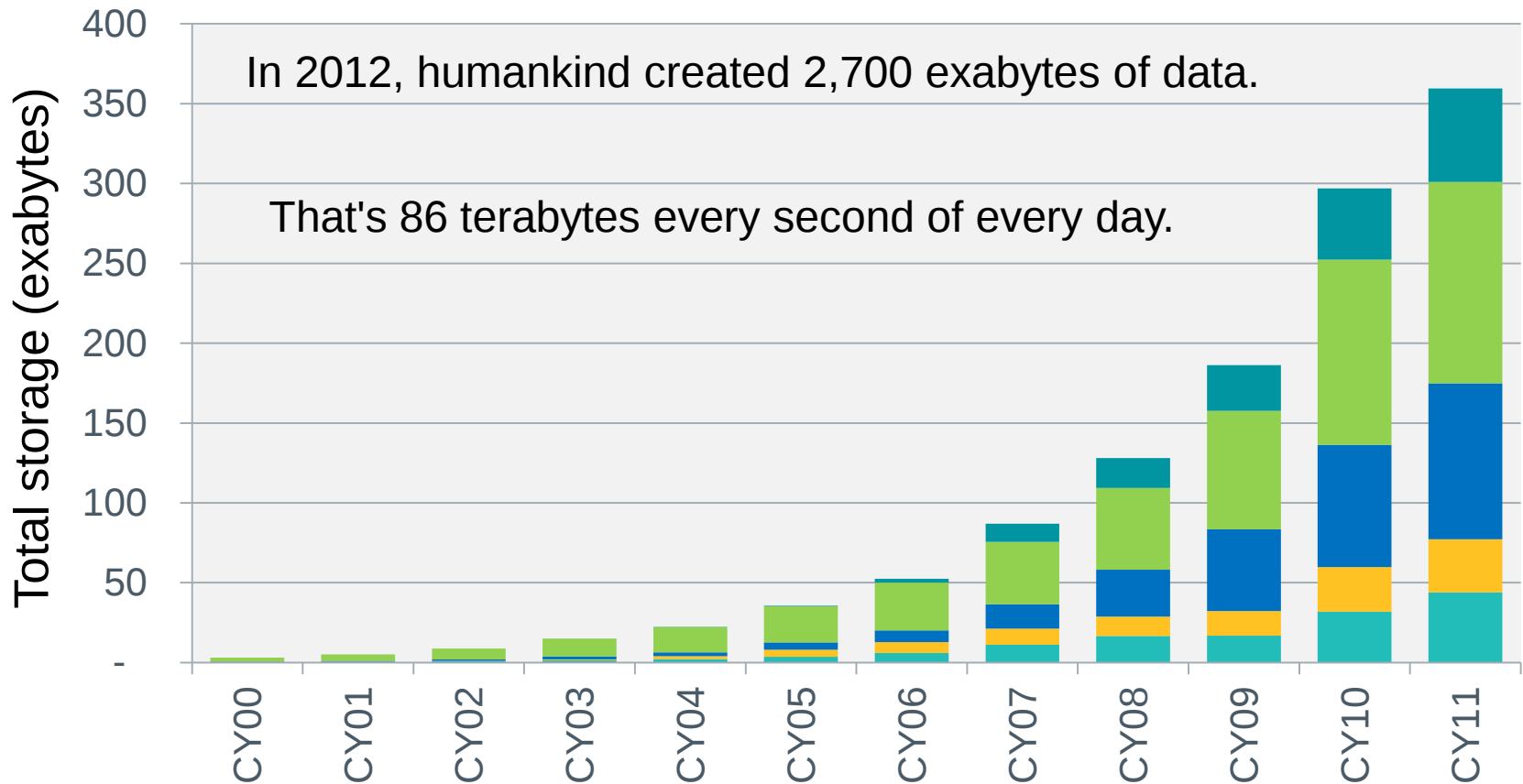
Samsung 2011



Cell Size: $0.0092 \mu\text{m}^2$ ($\sim 10^8$)
20 nanoseconds ($\sim 10^3$)
Volatile
Cost: \$0.25/gigabit

Total hard-drive capacity

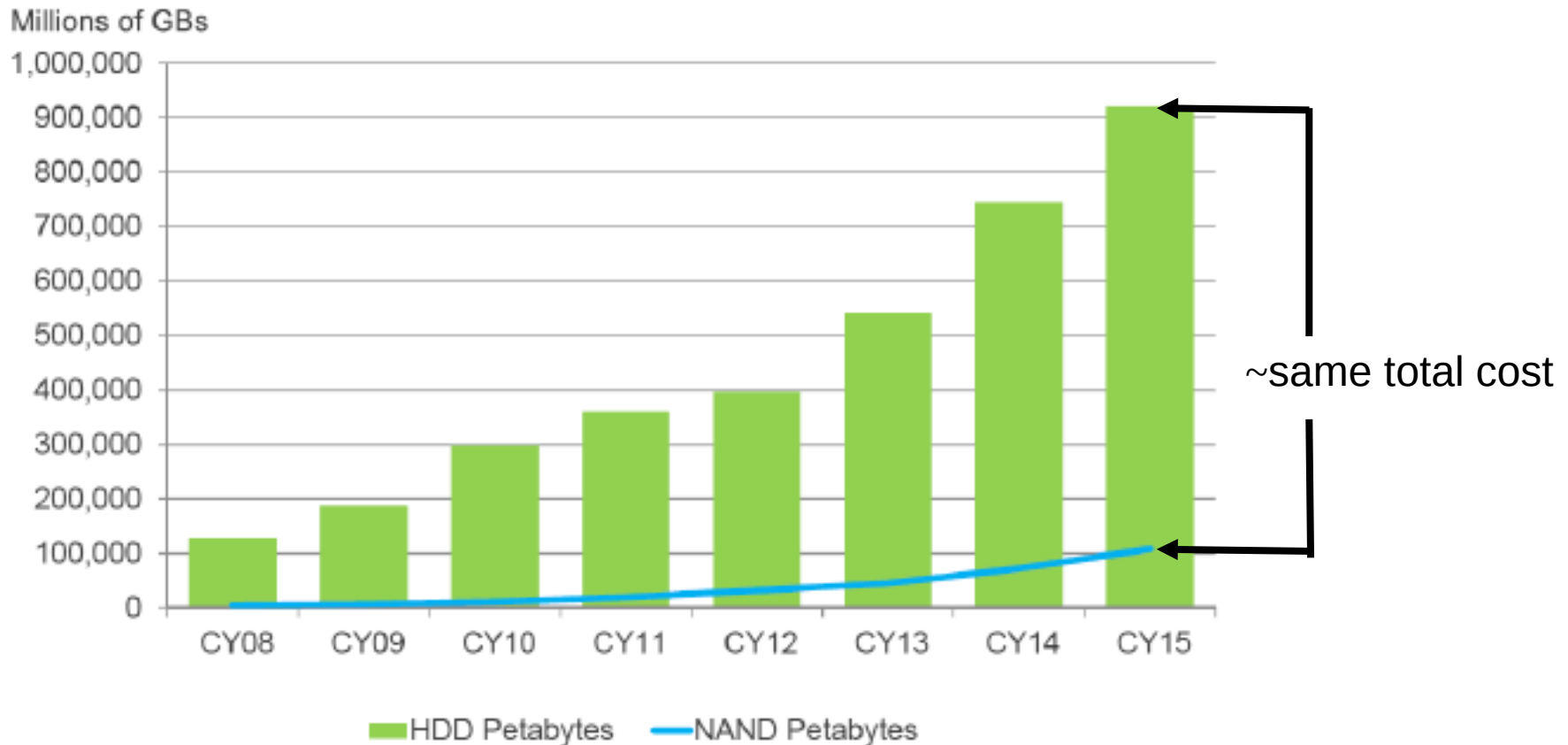
Exabyte = 1 million terabytes or 1 billion gigabytes or



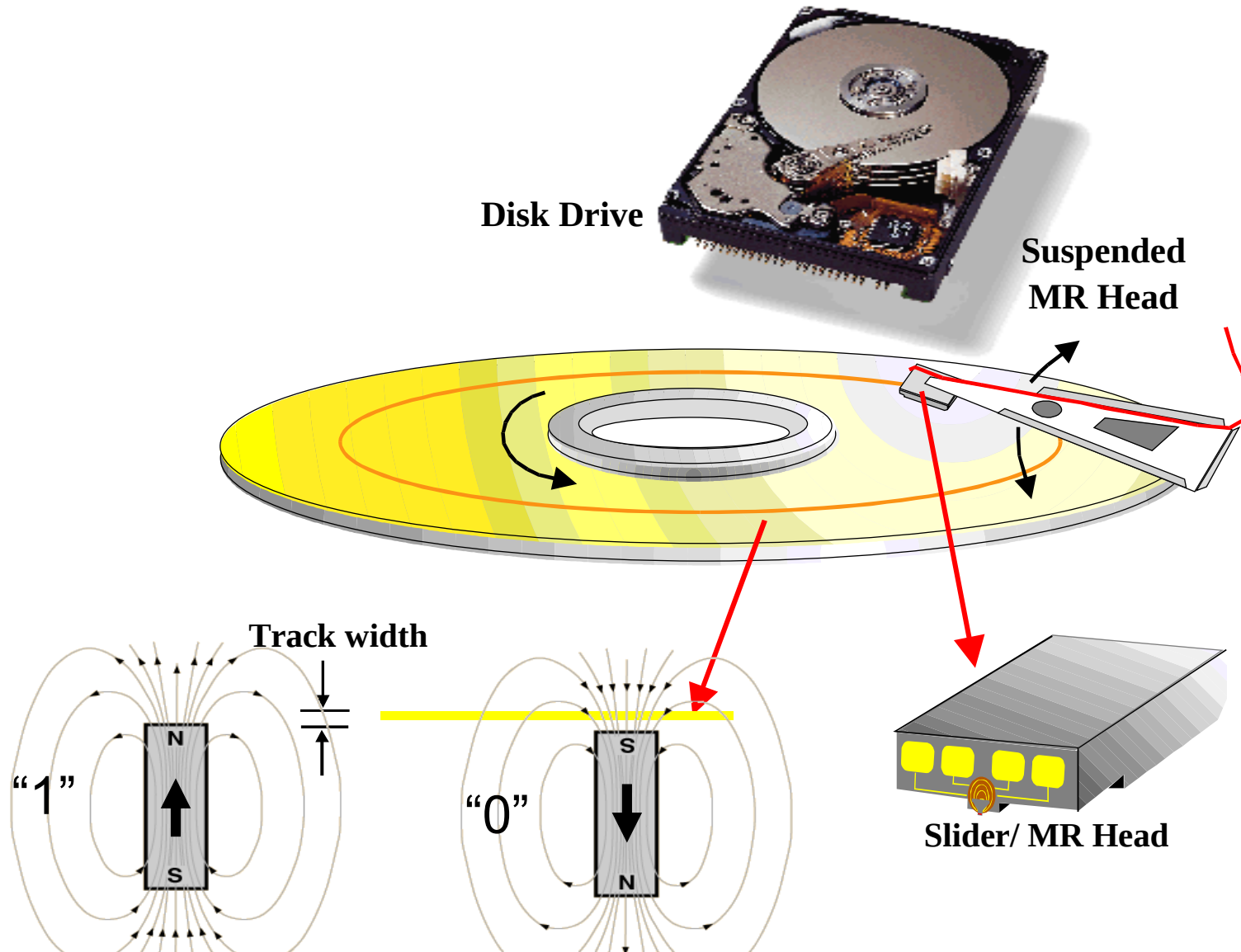
Source: Seagate Market & Competitive Intelligence

Enterprise Consumer Electronics Mobile PC Deskbased PC Retail

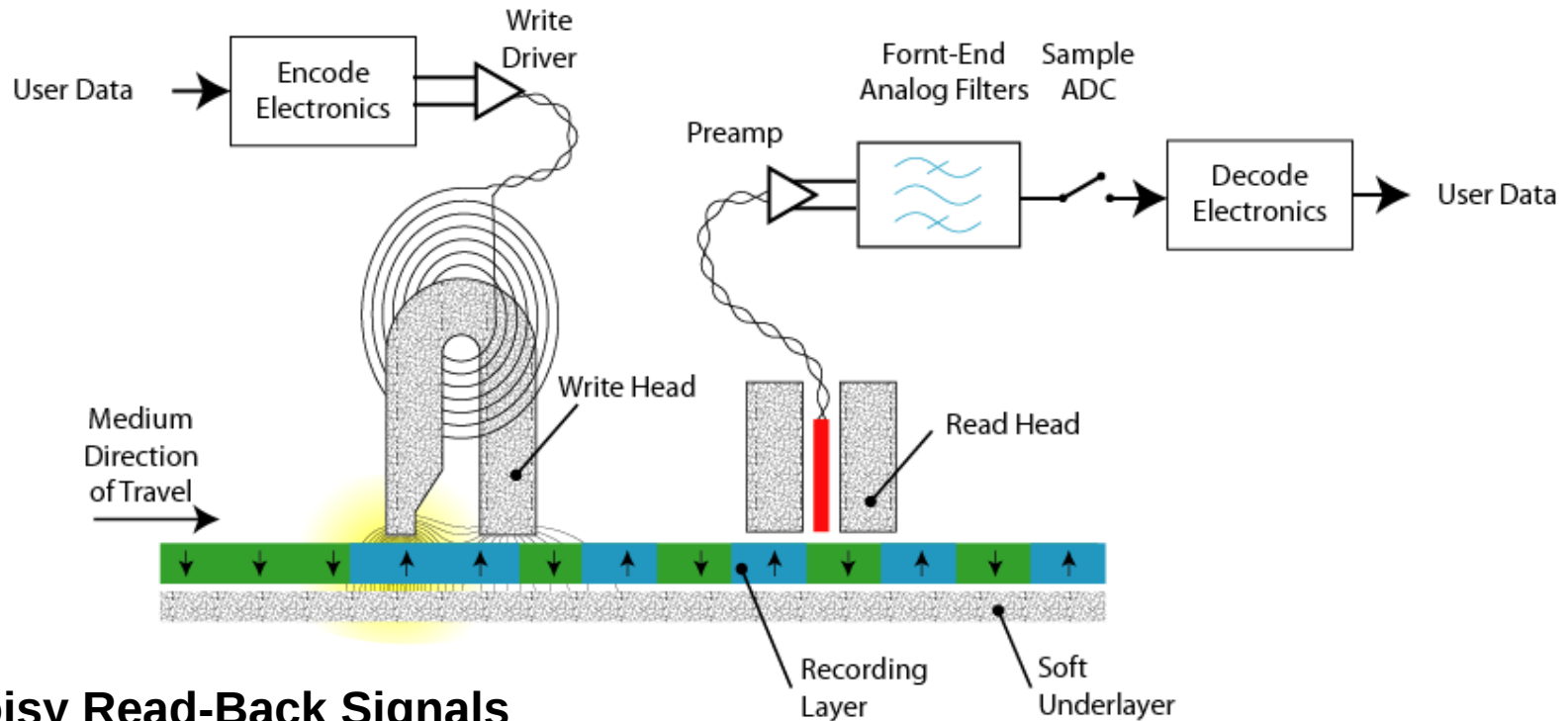
Hard-drives vs. solid state drives



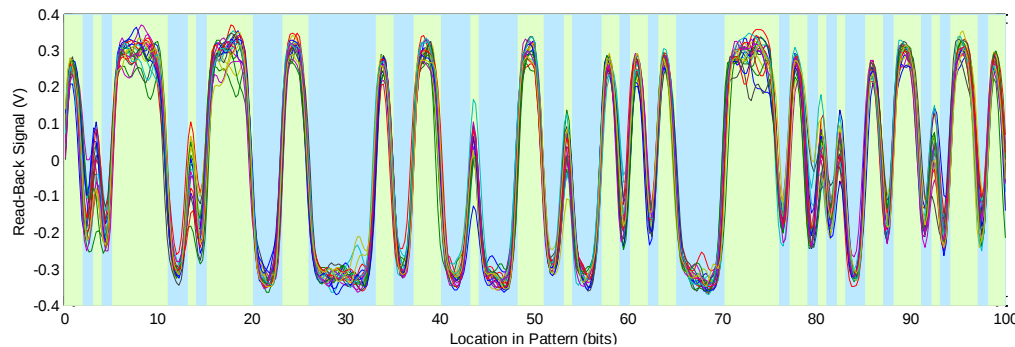
Disk drive basics



Magnetic recording



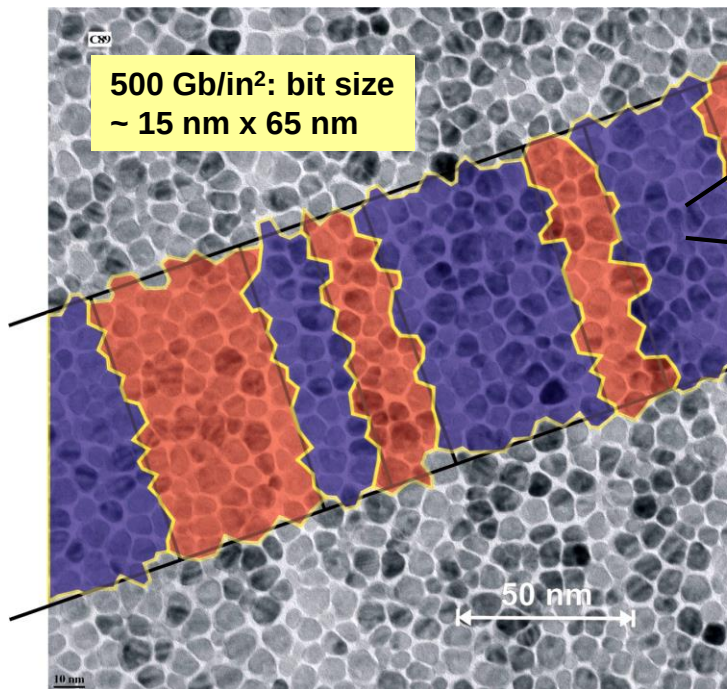
Noisy Read-Back Signals



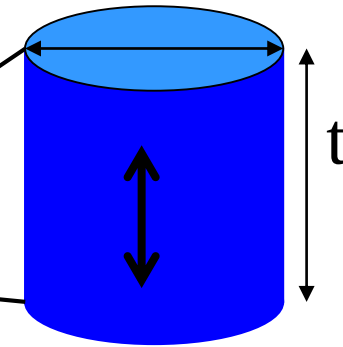
Media and the superparamagnetic effect

The edges of each recorded bit
follow the grain boundaries

→ transition noise



D



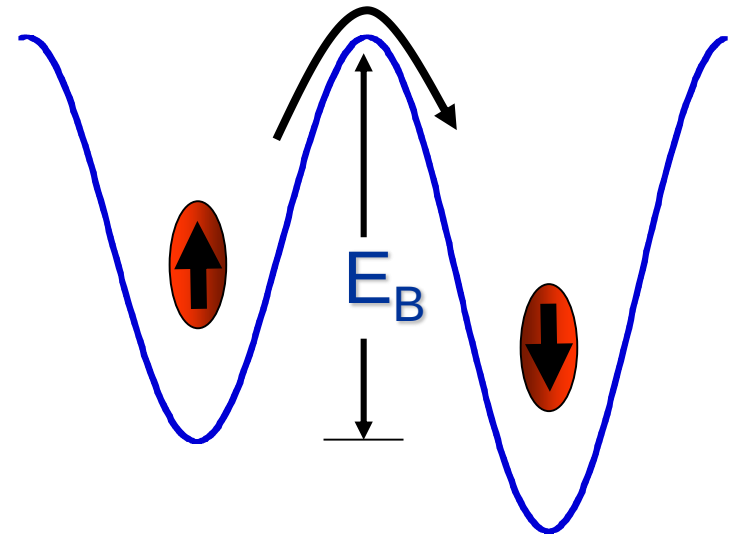
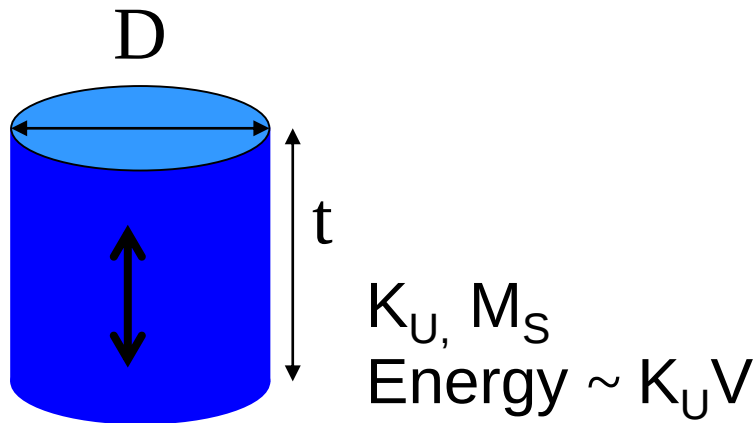
$$M_S, K_U, V$$
$$\text{Energy} = K_U V$$

Independent grains $\text{SNR} \sim \sqrt{N}$
want small V

$$\text{Energy/grain } K_U V > 50 k_B T$$

→ Scale media microstructure together
with rest of recording system

Media and the superparamagnetic effect



$$\tau \sim \tau_0 \exp(E_B/k_B T)$$

$\nwarrow$ 0.1 ns

$$K_U V = 100 k_B T$$

$$K_U V = 45 k_B T$$

$$K_U V = 25 k_B T$$

$$\tau > \text{age of the universe}$$

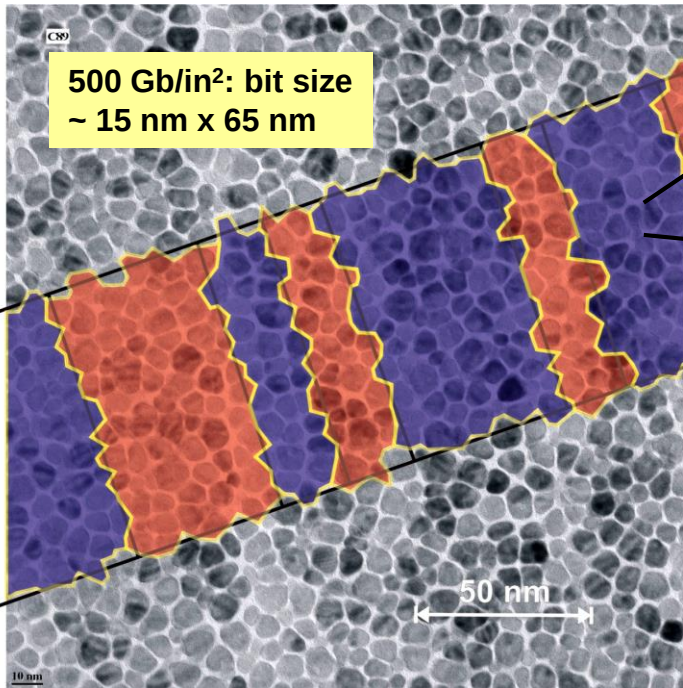
$$\tau \sim 10 \text{ years}$$

$$\tau \sim 7 \text{ seconds}$$

Media and the superparamagnetic effect

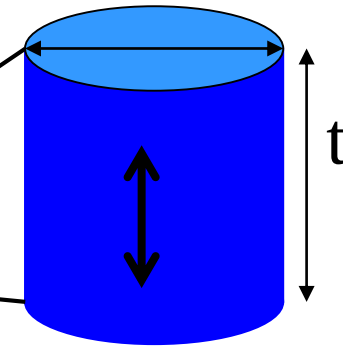
The edges of each recorded bit
follow the grain boundaries

→ transition noise



→ Scale media microstructure together
with rest of recording system

D



M_S, K_U, V
Energy = $K_U V$

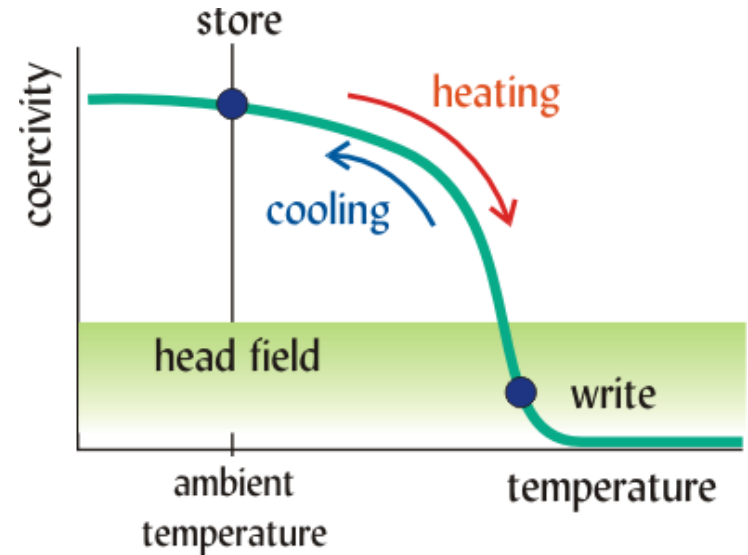
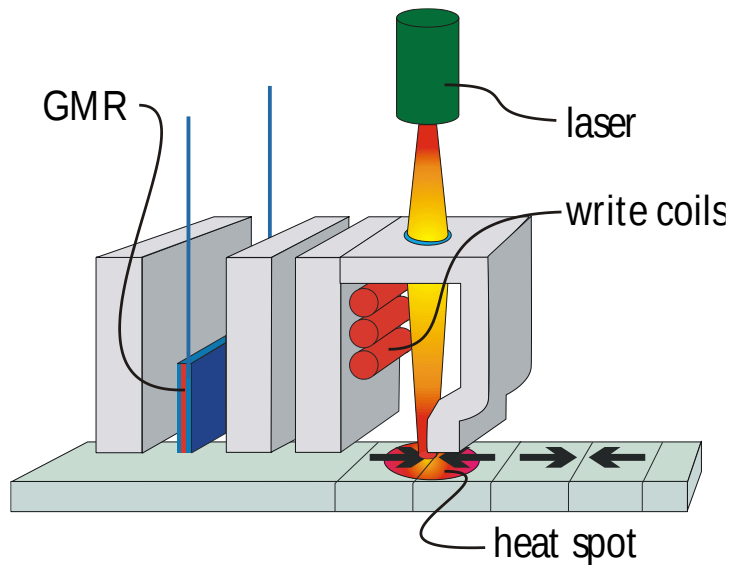
Independent grains $SNR \sim \sqrt{N}$
want small V

Energy/grain $K_U V > 50 k_B T$

$H_C = K_U / M_S < H_{\text{write-head}}$

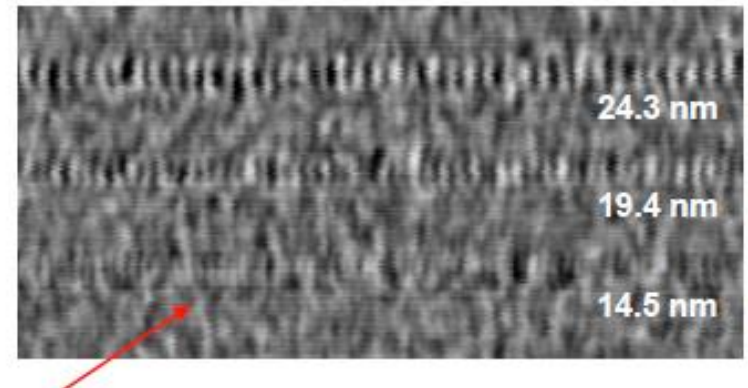
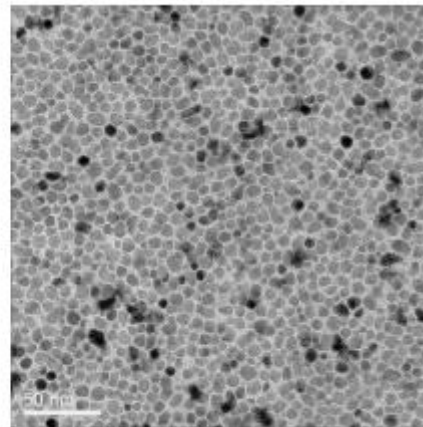
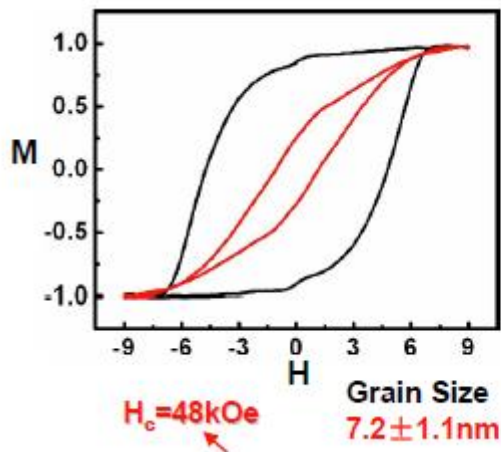
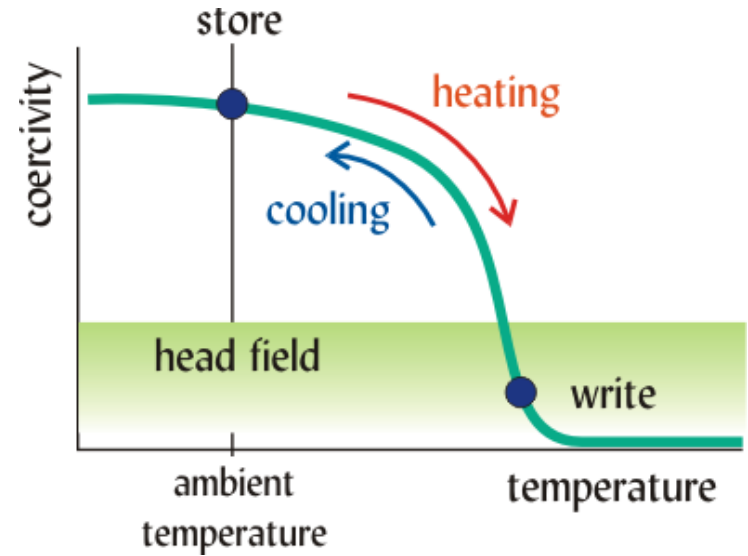
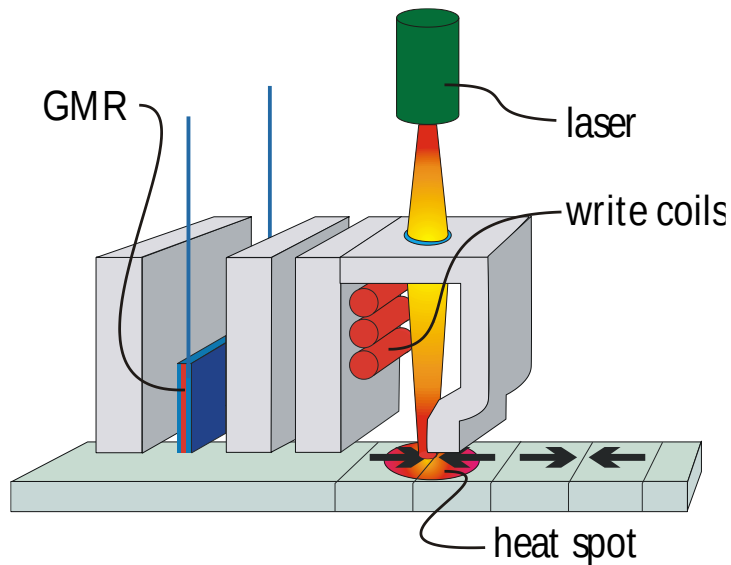
Competition for reading, writing and
storing data: superparamagnetic effect

Heat-assisted recording



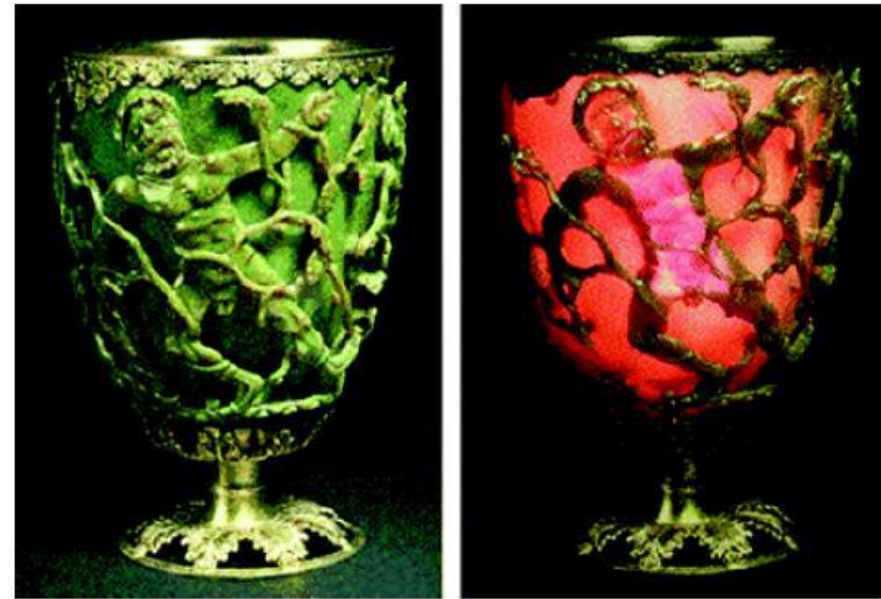
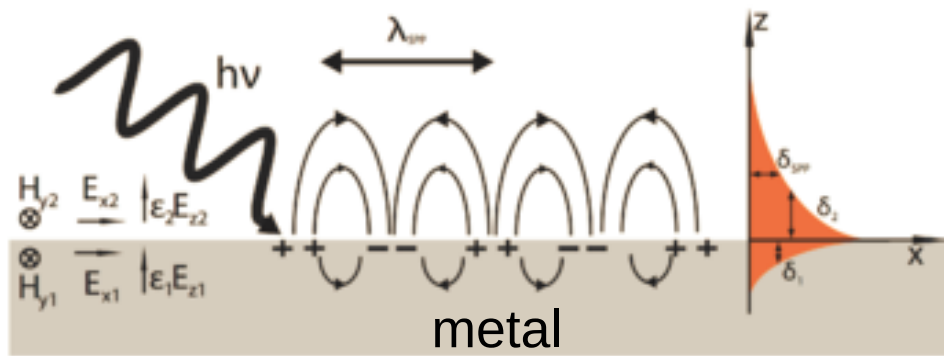
- <50-nm heat spot, $\sim 300^\circ\text{C}$ rise/cool in 1 ns integrated into a head
- A magnetic media w/ high K_U , small grains and high dH_K/dT
- A head-disk interface (i.e. lubricant) that can handle repeated heating

Heat-assisted recording



Plasmonics

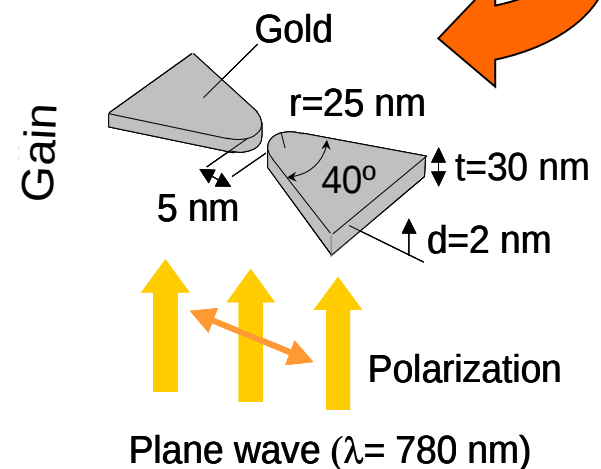
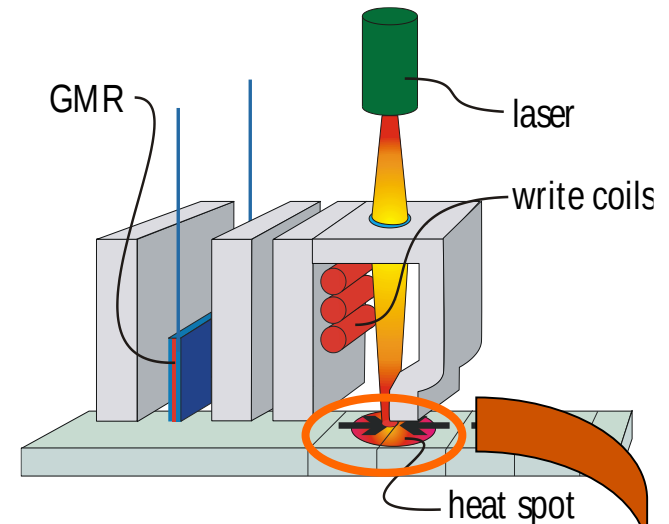
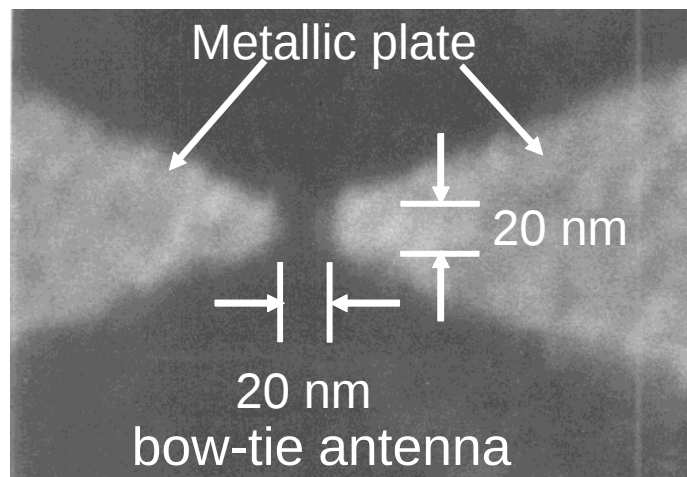
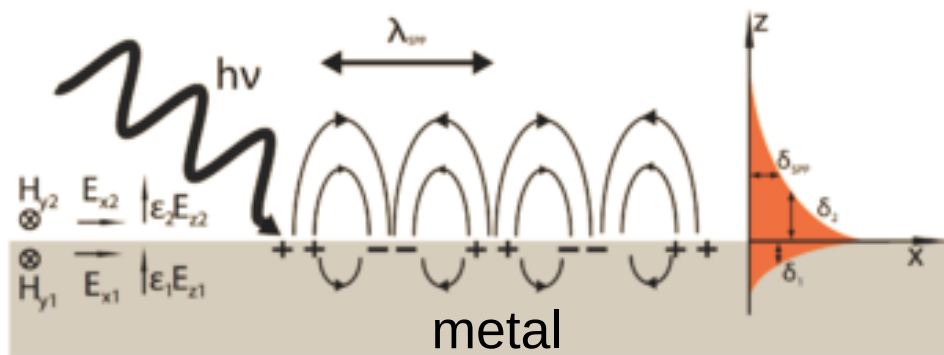
Surface plasmons



Lycurgus Cup - 4th Century Roman

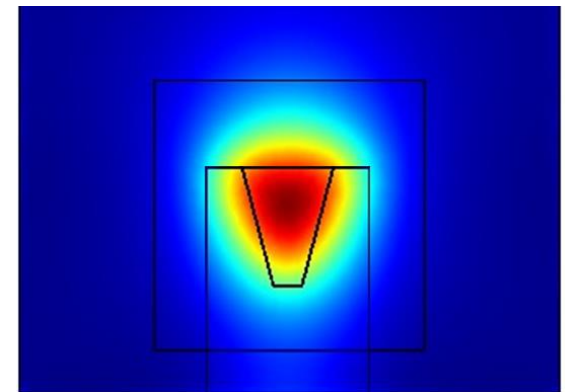
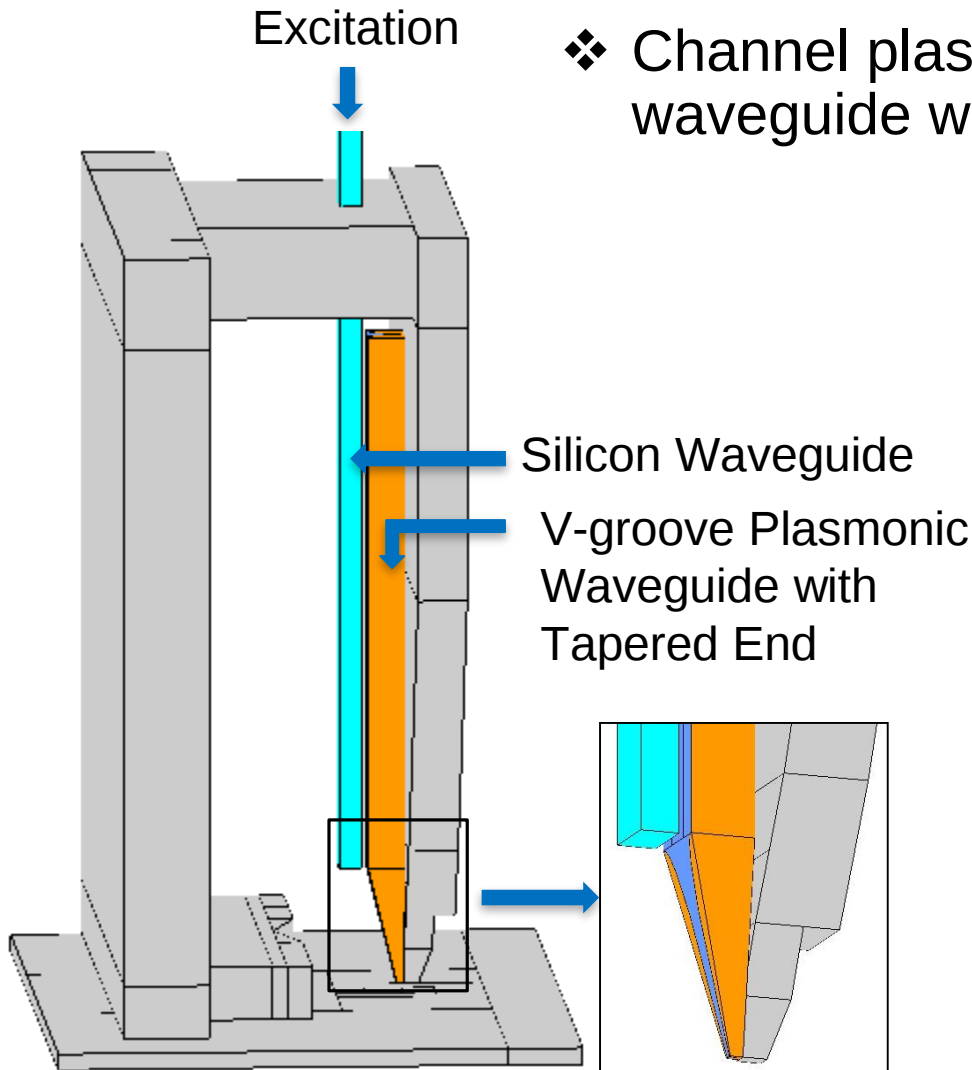
Plasmonics

Surface plasmons

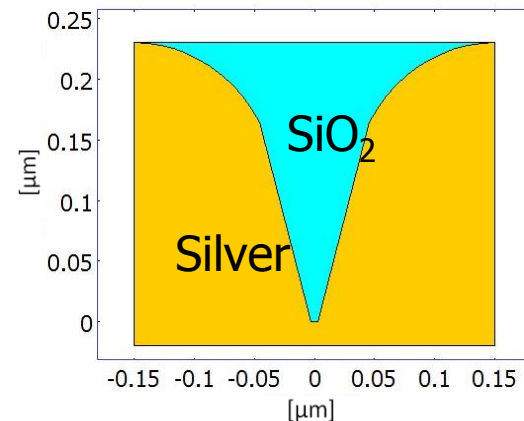


Advanced optical guides

❖ Channel plasmon polariton (CPP) waveguide with V-groove



FWHM: 31nm x 32nm
Efficiency with silver: 20%

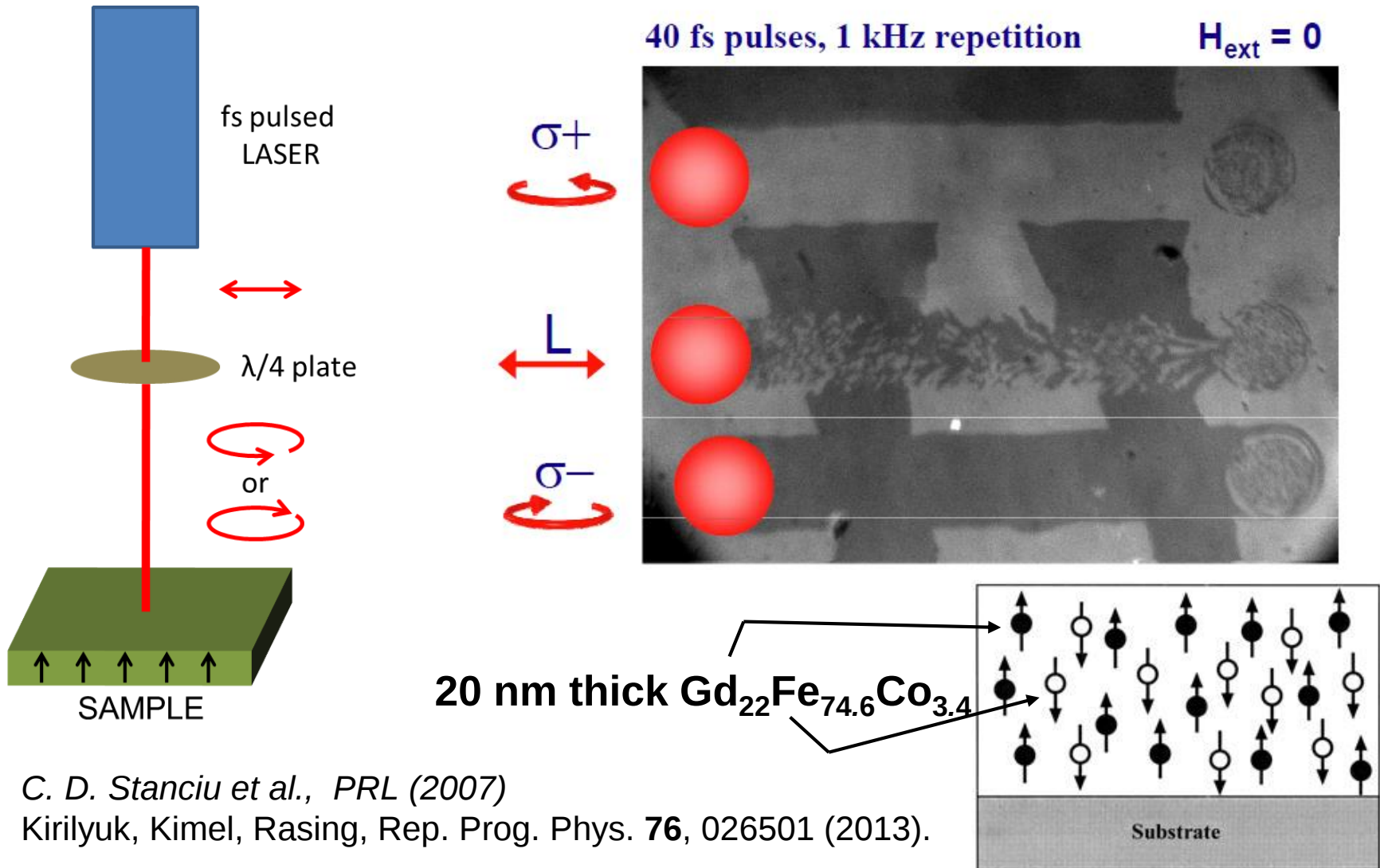


V. Lomakin

All-optical recording?

Directly control magnetism with light?

All-optical recording?



C. D. Stanciu et al., *PRL* (2007)

Kirilyuk, Kimel, Rasing, *Rep. Prog. Phys.* **76**, 026501 (2013).

All-optical switching (AOS)

What are the origins?

- Is GdFeCo unique?
- Is heat required?
- Is it an ultra-fast process?
- Is angular momentum of the light important?

For applications

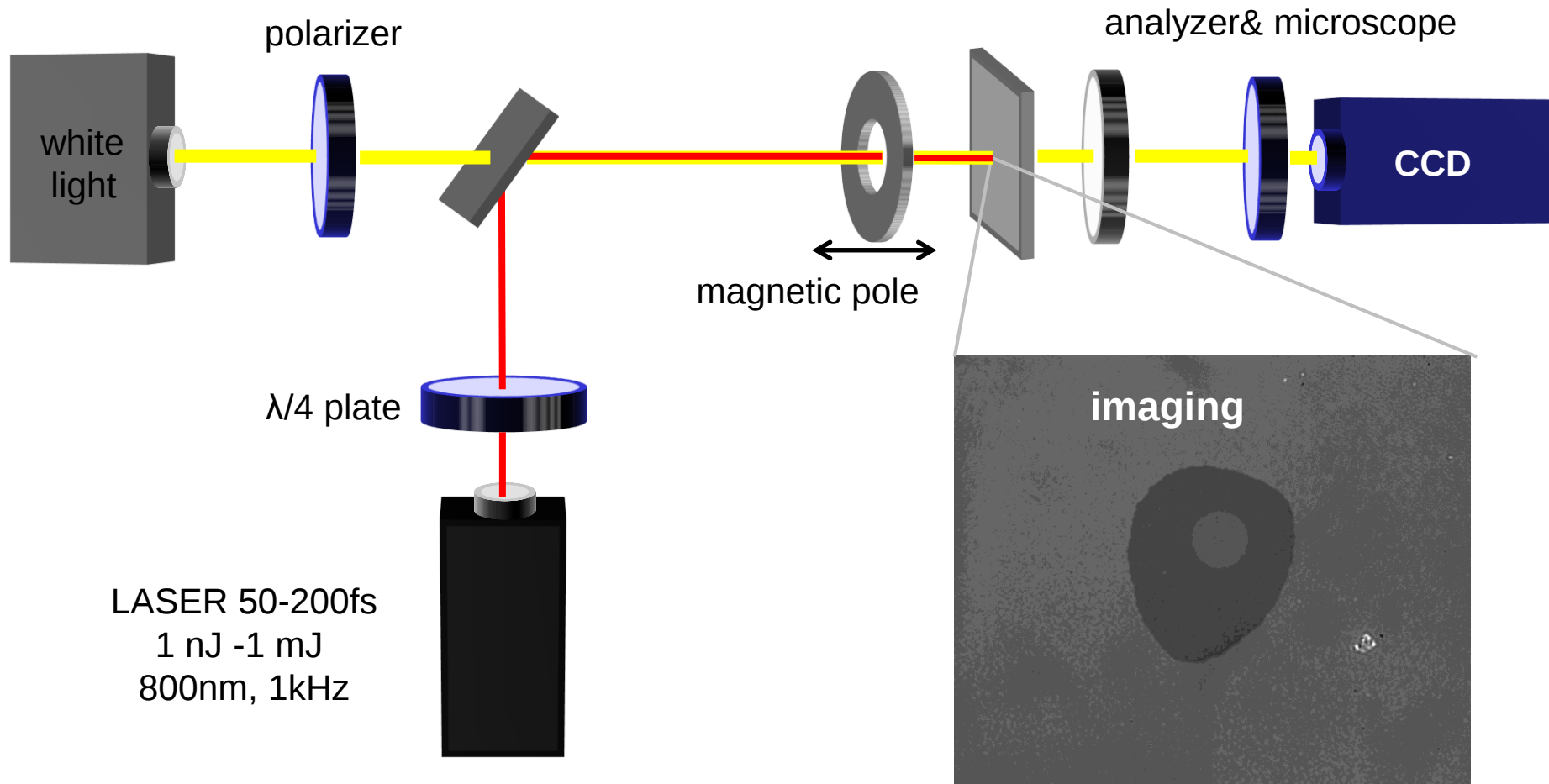
- Higher anisotropy
- Ferromagnetic recording media

Materials study of AOS

Broaden the materials space: >1000 samples

- **RE-TM alloys and multilayers**
- **Heterostructures**
- **Nanostructures**

UCSD experimental facility

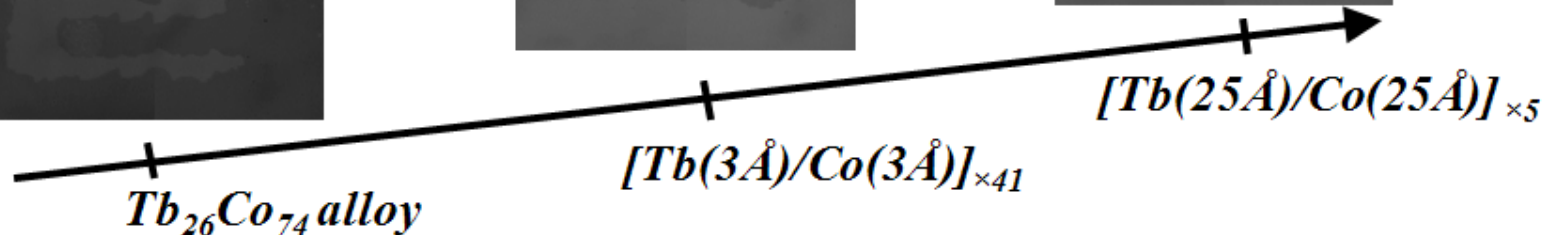
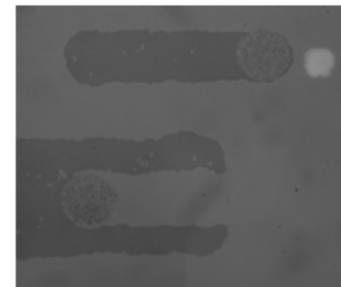
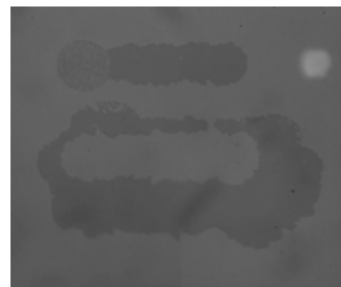
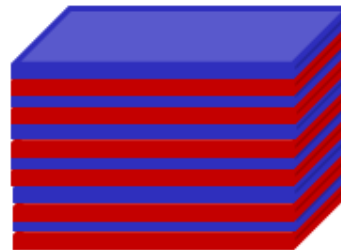
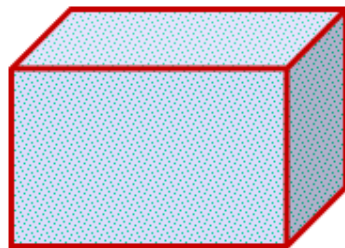


TbCo film

Materials study of AOS

* Lanthanide series

lanthanum 57 La 138.91	cerium 58 Ce 140.12	praseodymium 59 Pr 140.91	neodymium 60 Nd 144.24	promethium 61 Pm [145]	samarium 62 Sm 150.36	europium 63 Eu 151.96	gadolinium 64 Gd 157.25	terbium 65 Tb 158.93	dysprosium 66 Dy 162.50	holmium 67 Ho 164.93	erbium 68 Er 167.26	thulium 69 Tm 168.93	ytterbium 70 Yb 173.04
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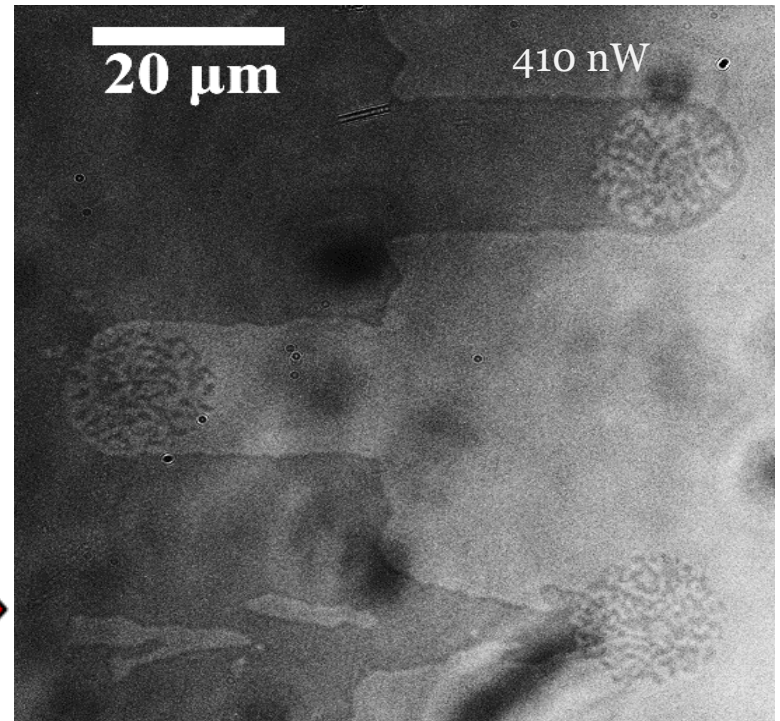
All-optical switching

Rather general property of ferrimagnets

Nature Materials **13**, 286-292 (2014)

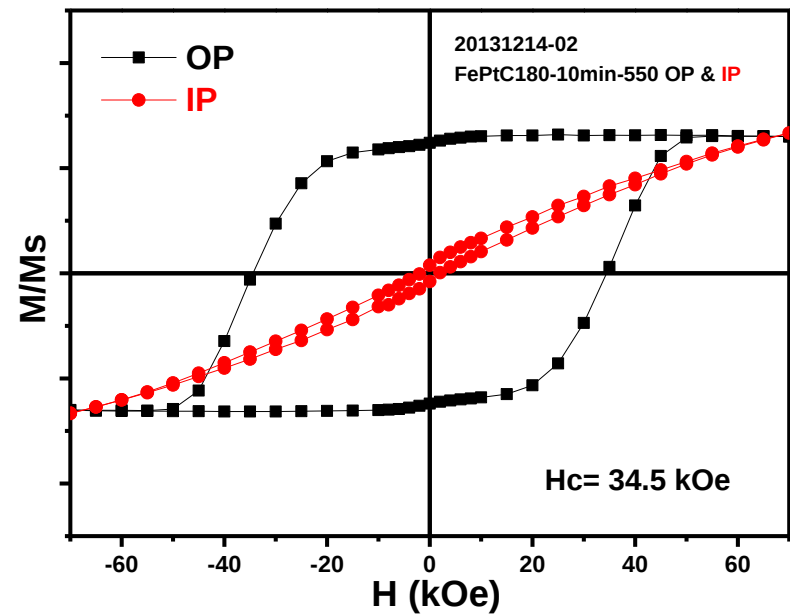
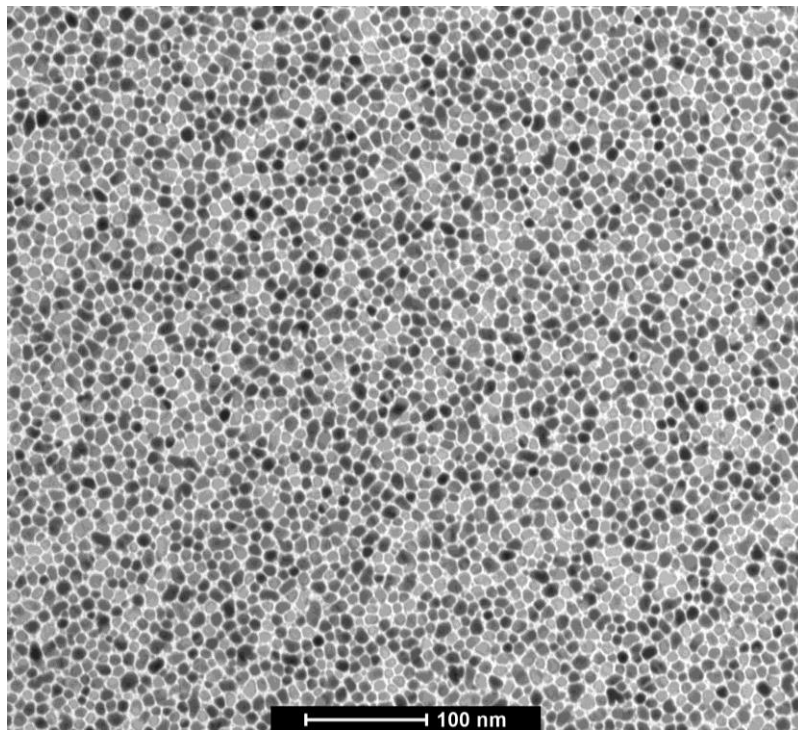
Can it also work
with ferromagnets?

Can it work with
magnetic recording
media?



Ferromagnets

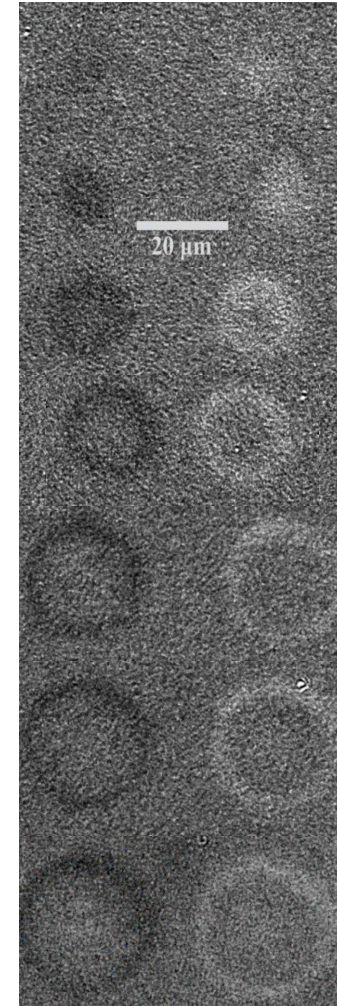
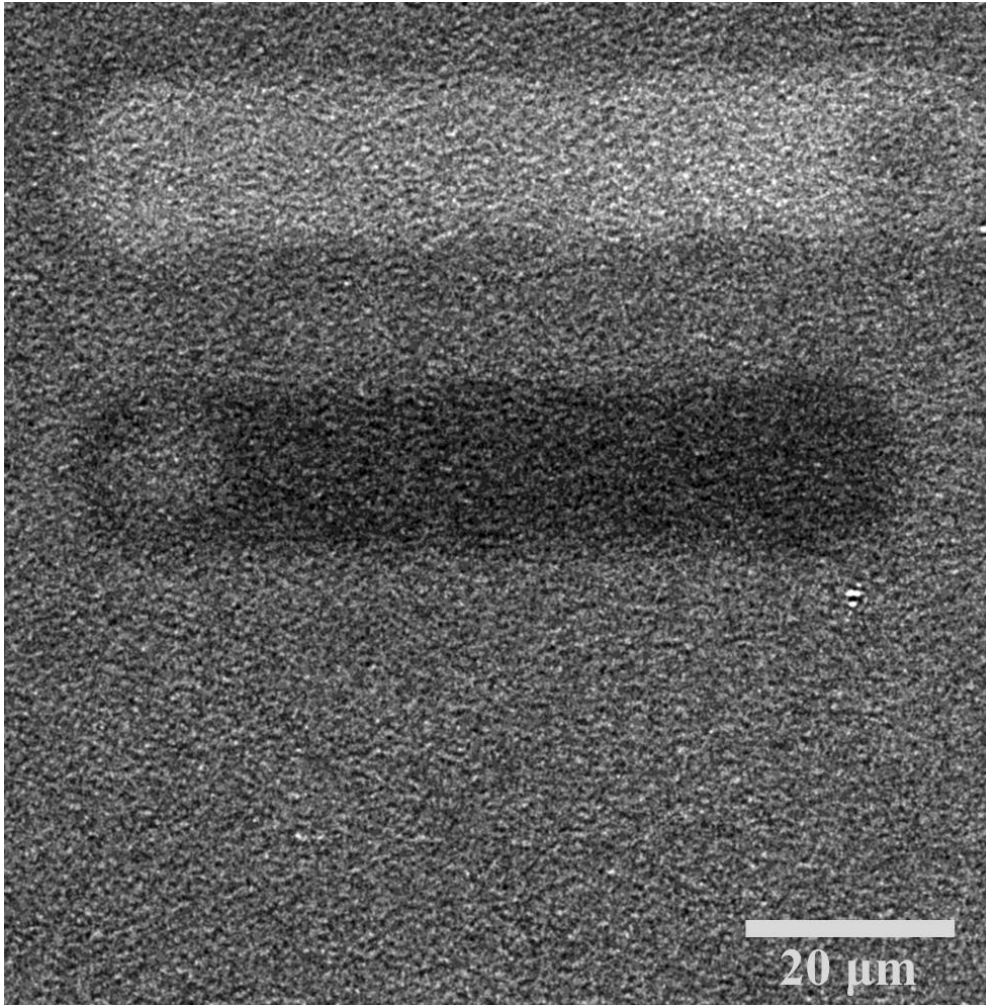
15-nm FePt-C and FePtAg-C granular films



8 nm grains with 11 nm separation

Ferromagnets

15-nm FePt-C granular films



423

490

601

724

1012

1256

1395 nW

Ferromagnetic AOS

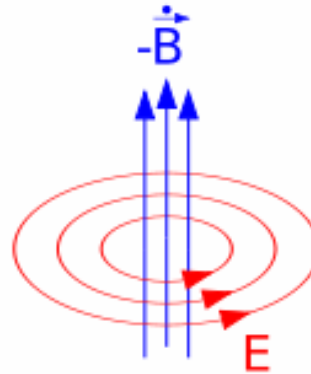
Heating by the laser near T_C



Magnetic field/Angular momentum from a laser beam

Inverse Faraday effect

$$\vec{H}_{eff} = \frac{\epsilon_0}{\mu_0} \alpha \underbrace{\left[\vec{E}(\omega) \times \vec{E}^*(\omega) \right]}_{\text{circular polarization}}$$



Suppression of domain formation during cooling
thin film, high anisotropy and/or low M

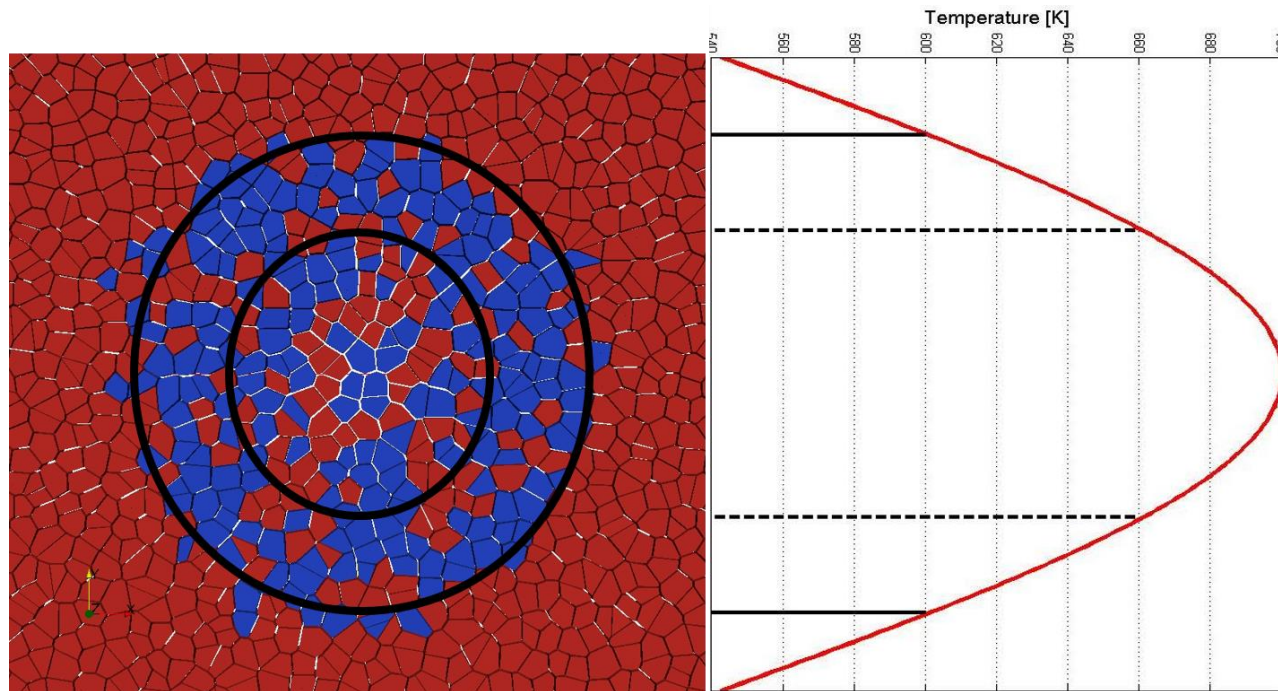
Landau–Lifshitz–Bloch simulations

Marco Menarini and Vitaliy Lomakin, UC San Diego

Landau-Lifshitz-Bloch simulations

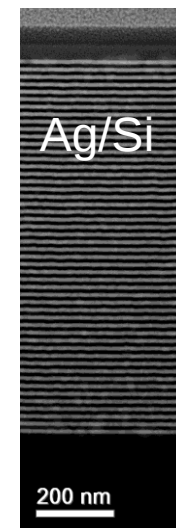
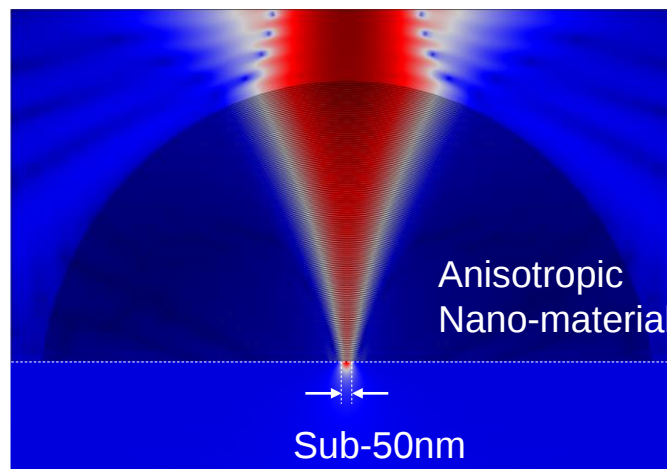
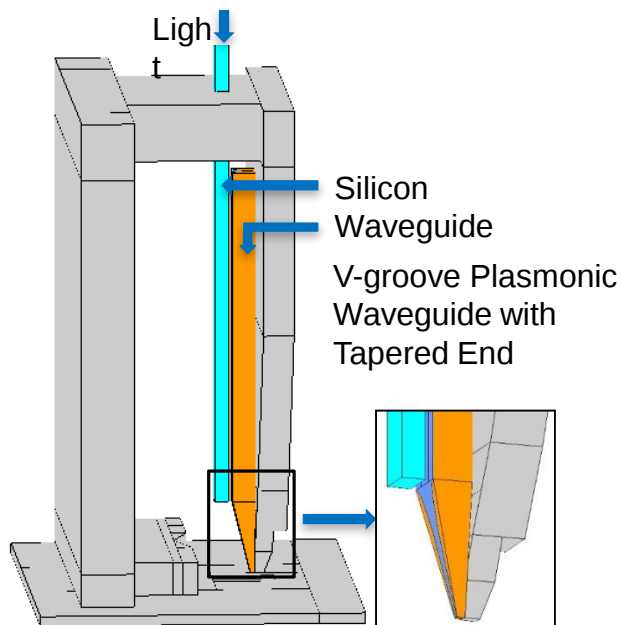
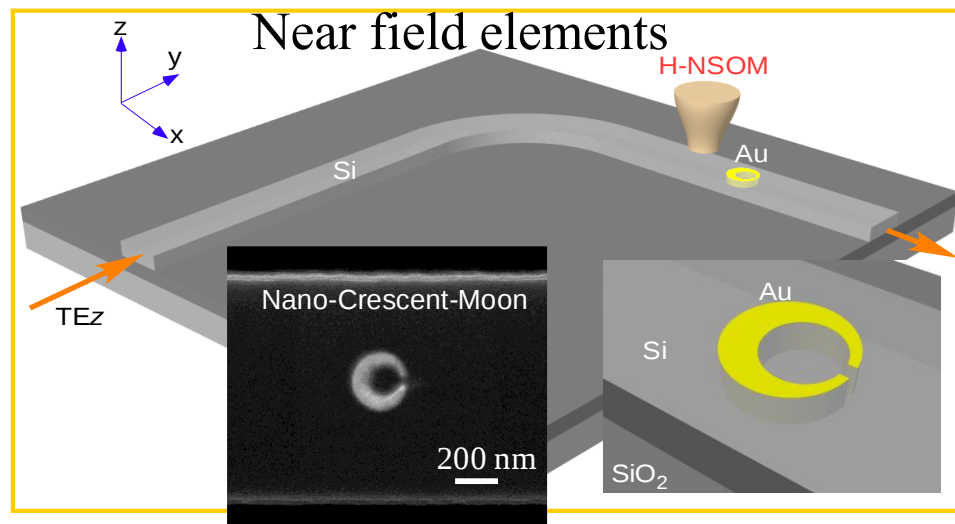
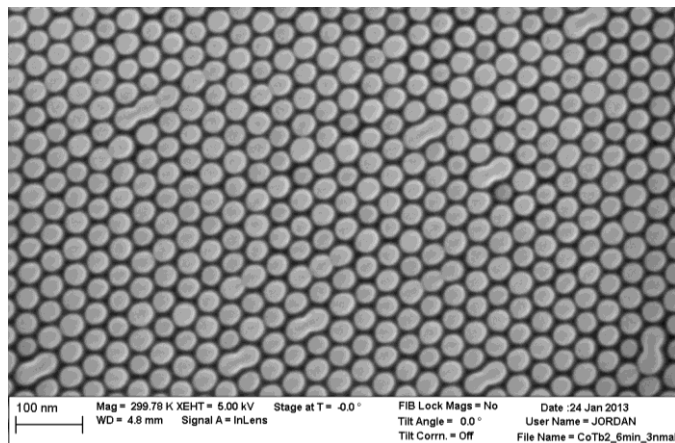
Pulse Length 1ps with a pulse field intensity 2T

Maximum Temperature $T=700$ K and $T_c=660$ K



Future of all-optical switching?

Nano-scaled islands



Leveraging the hard drive for memory

Return of magnetism in memory and processing?

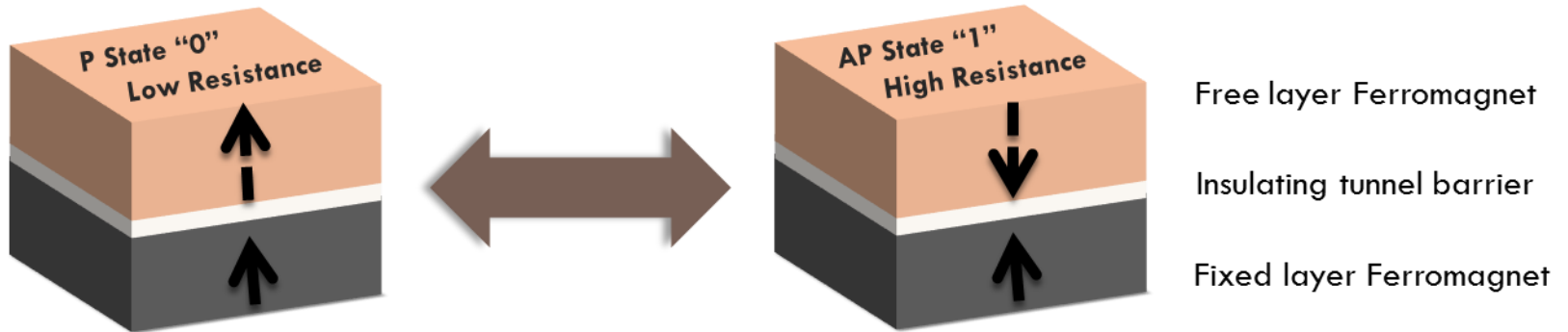
Advantages of magnetism

- Non-volatile ($E_B > 50 k_B T$)
- Low energy $50 k_B T = 0.2 \text{ aJ}$

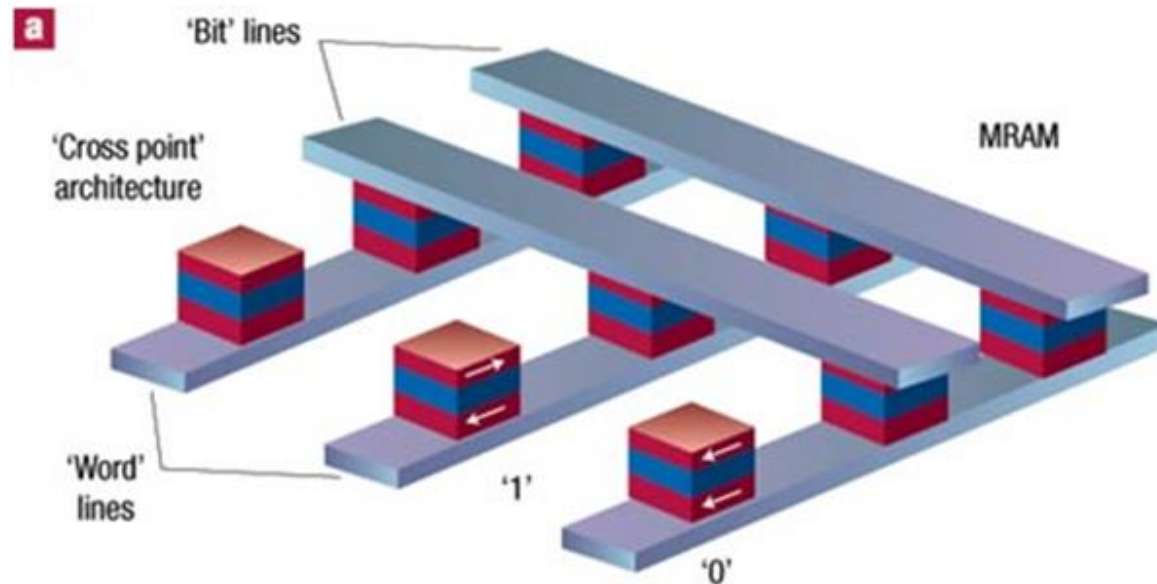
Performance and power issues in IT

- Memory is a bottleneck (data-centric vs. compute centric)
- Hand-held devices are increasingly power limited
- computing and data centers dissipate Megawatts of power
- Opportunities for new non-volatile memories

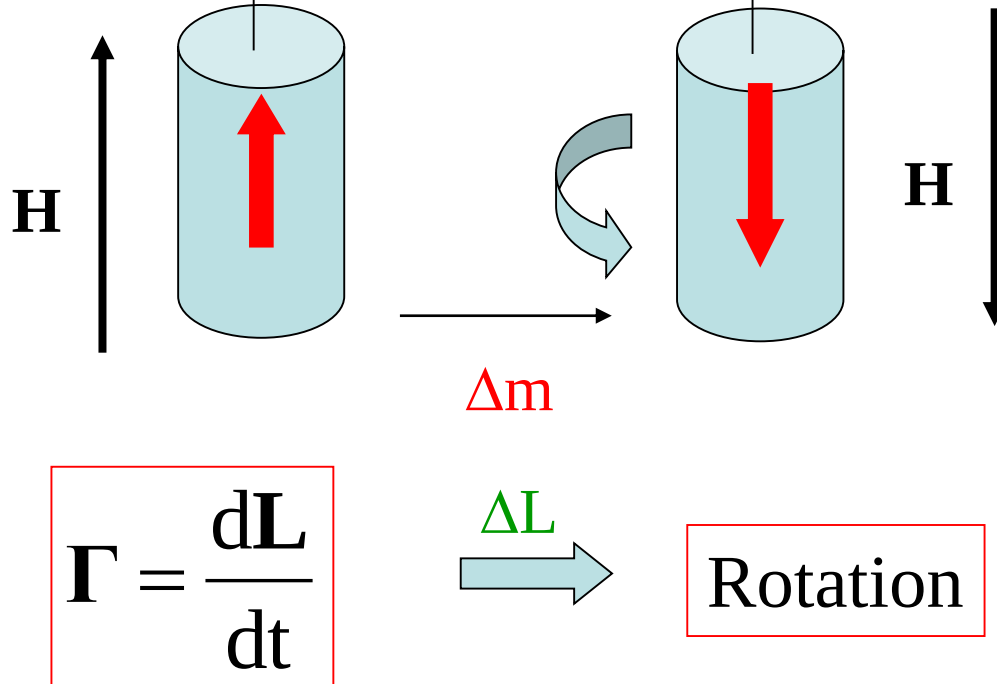
Magnetic RAM



Nobel Prize in physics in 2007



Einstein de Haas effect

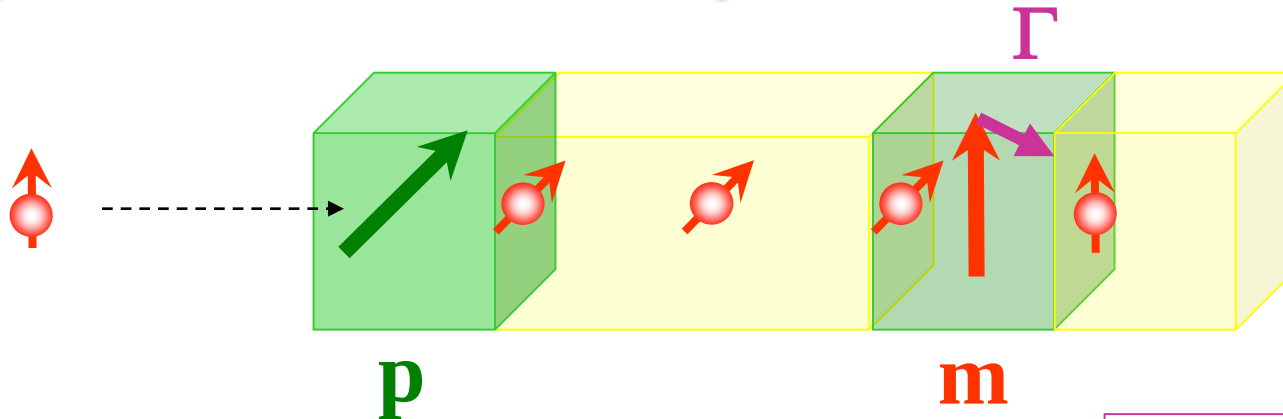


A. Einstein, W. J. de Haas, *Experimenteller Nachweis der Ampereschen Molekularstörme*, Deutsche Physikalische Gesellschaft, Verhandlungen **17**, pp. 152-170 (1915).

Proof of the existence of the Ampere molecular field

“how treacherous nature is, when you have to deal with it experimentally”

Spin transfer torques



Angular momentum conservation
→ spin transfer torques

$$\mathbf{\Gamma}_m = \frac{d\mathbf{L}_e}{dt}$$

J. Slonczewski, J. Magn. Magn. Mater. **159**, L1 (1996)

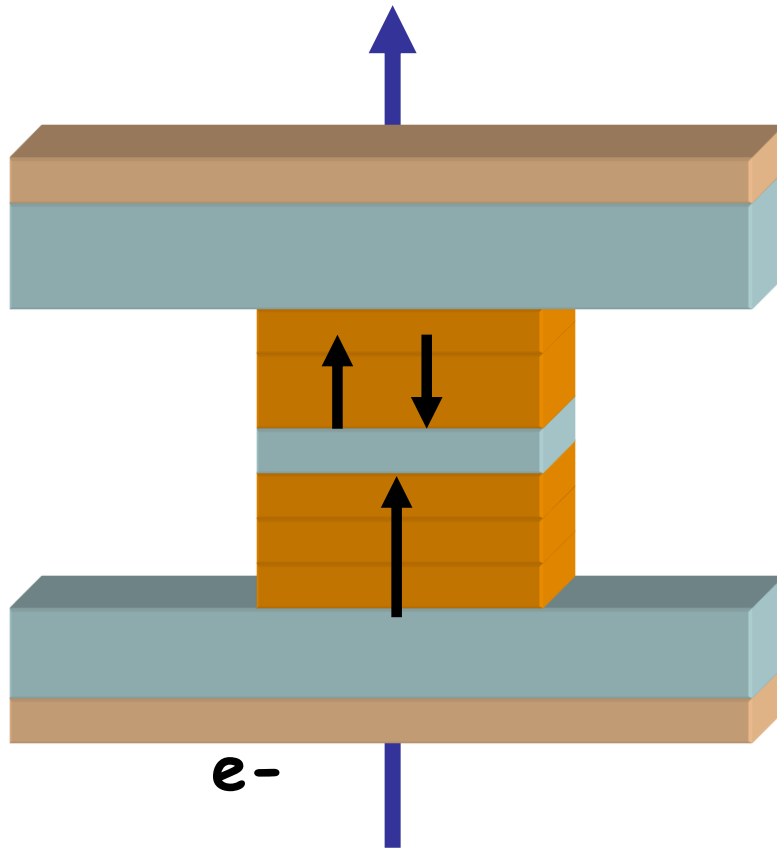
L. Berger, Phys. Rev. B **54**, 9353 (1996)

Katine *et al.*, PRL **84**, 3149 (2000)

see J. Magn. Magn. Mater. **320** (2008)

articles on spin torque edited by Stiles and Ralph

Perpendicular anisotropy devices

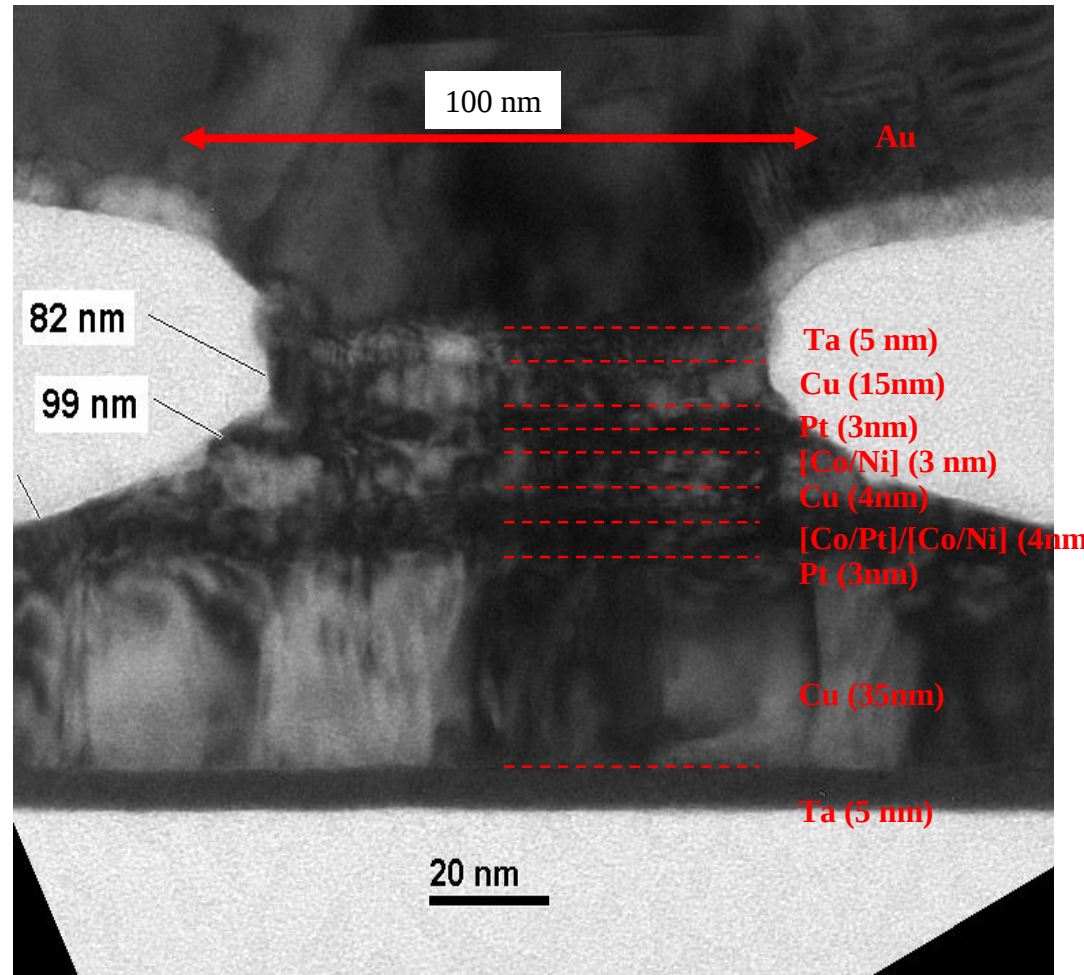
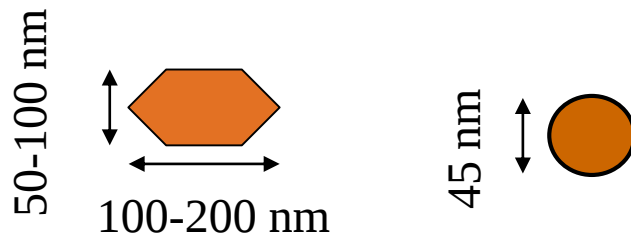
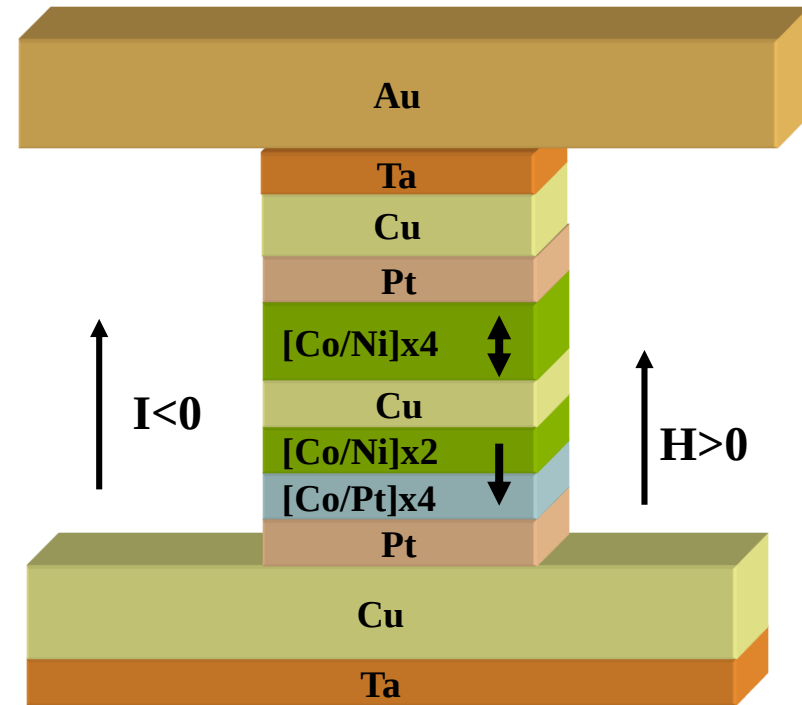


- Higher thermal stability
 - $E_B > 50 k_B T$
- More efficient reversal
 - I_C scales with E_B

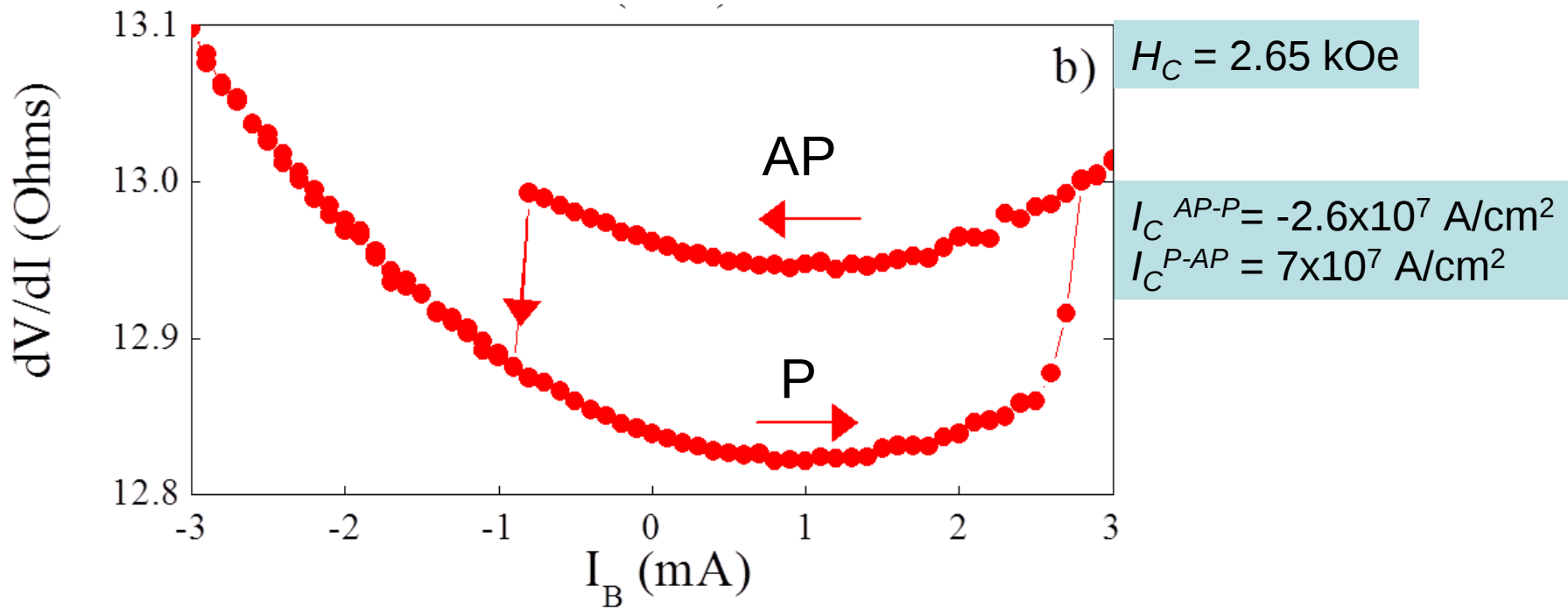
Mangin et al., Nature Mater. 5, 210 (2006)

Perpendicular devices

- Use of negative HSQ resist as a high fidelity mask
- ~1000 devices/5 inch wafer: circles and hexagons from 45nm to 1500nm

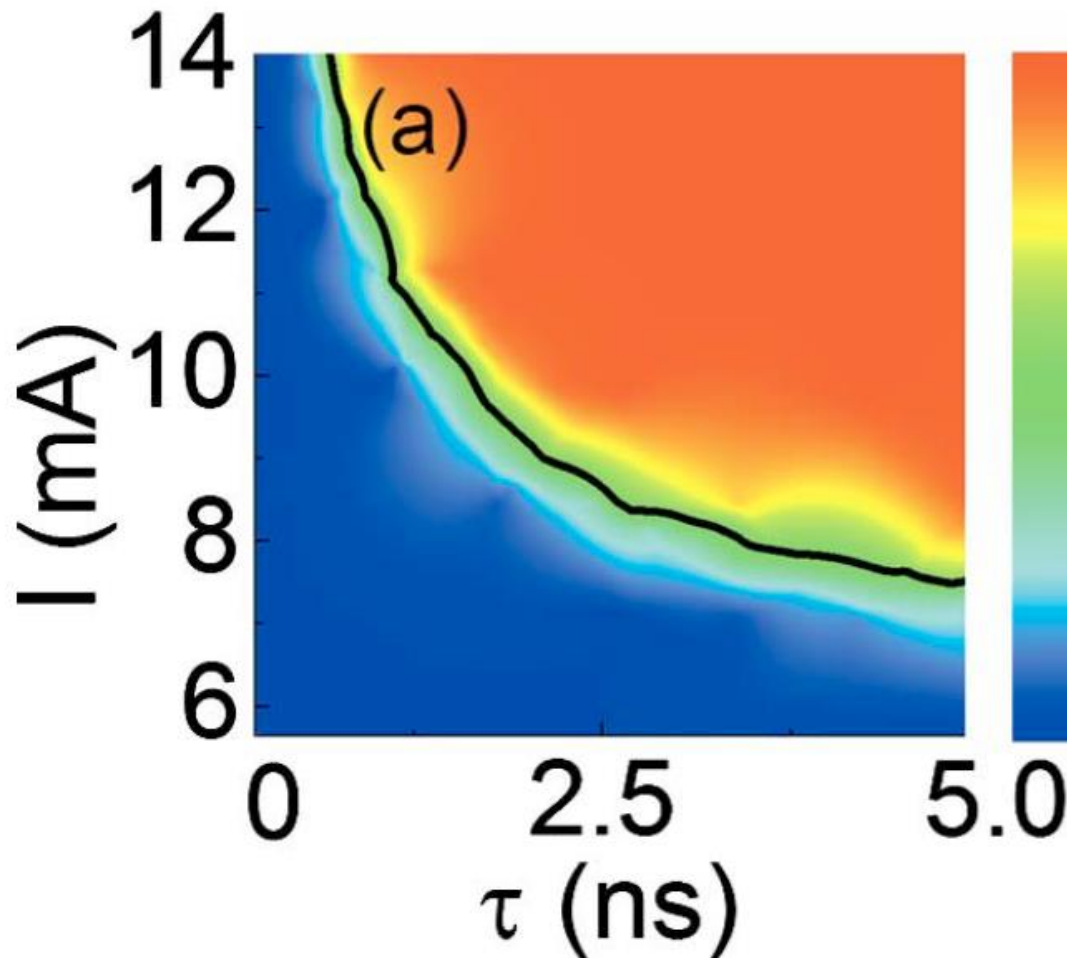


Current reversal in 50x100 nm² devices



Energy and time scales?

Time dependence and energy



$$1/\tau = A(I - I_{C0})$$

τ = reversal time

I = current

I_{C0} = critical current to
counter damping

A = dynamics parameter

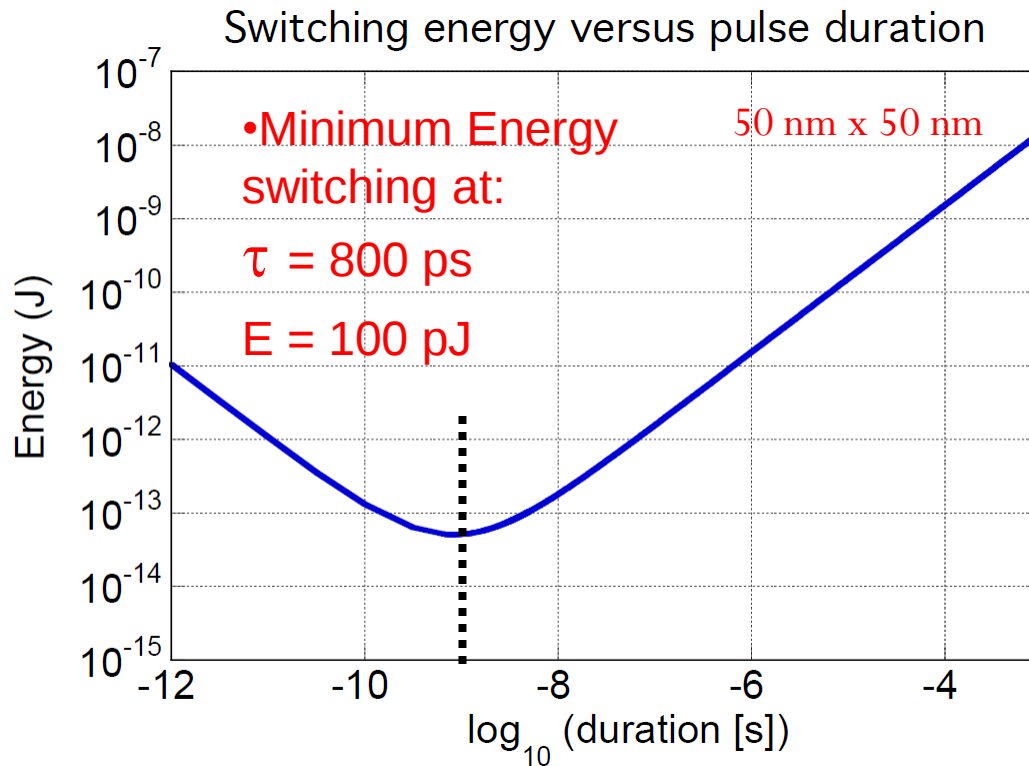
D. B. Bedau *et al.*, Appl. Phys. Lett. **96**, 022514 (2010)

D. Bedau, App. Phys. Lett. **97**, 262502 (2010)

H. Liu, et al., Phys. Rev. B **85**, 220405 (2012)

Minimum energy

$$E = I^2 R \tau \quad 1/\tau = A(I - I_{C0})$$



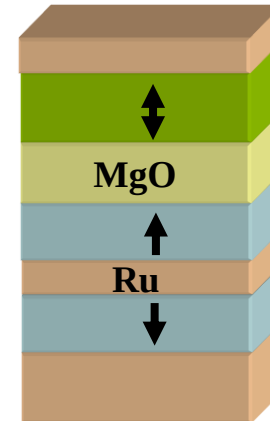
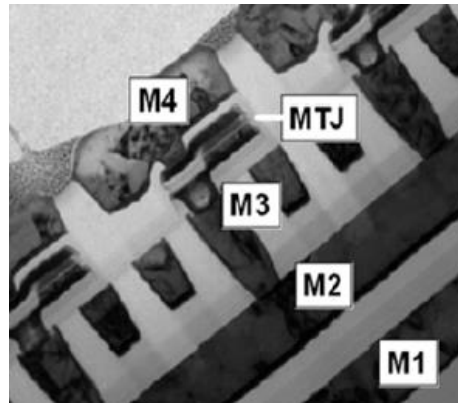
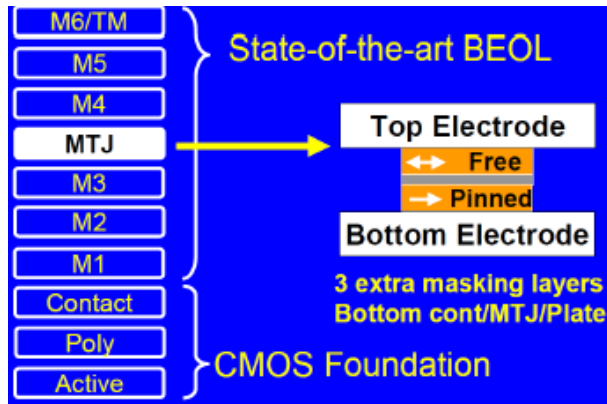
6×10^6 electrons

5×10^5 spins in the
free layer

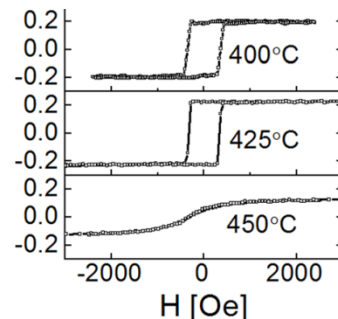
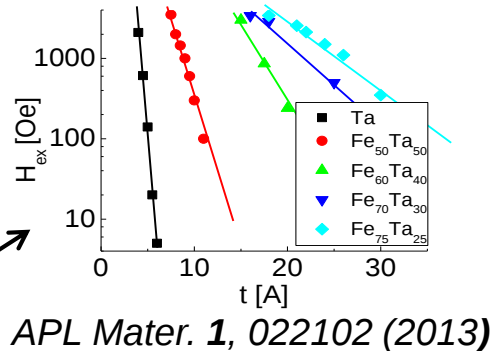
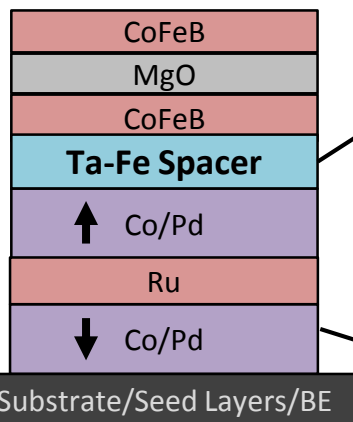
~14 electrons/spin

Energy in pulse is
 5×10^5 times E_B

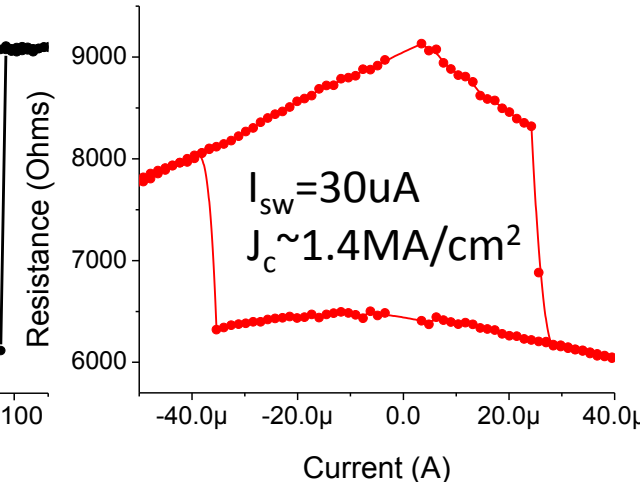
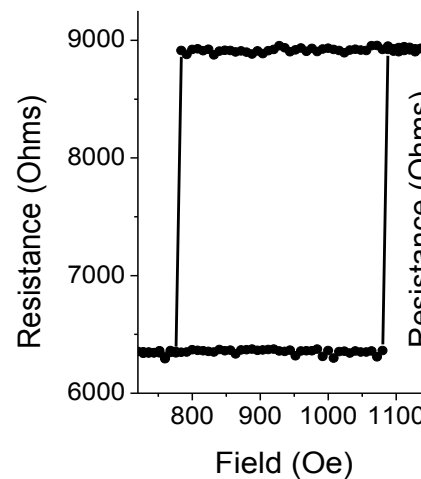
Perpendicular MRAM cells



High anisotropy
 $E_B > 50 k_B T$ (30 nm)
 High TMR
 Low I_C and V_C
 Symmetric I_C
 Low read current
 $T_{ann} = 400^\circ C$

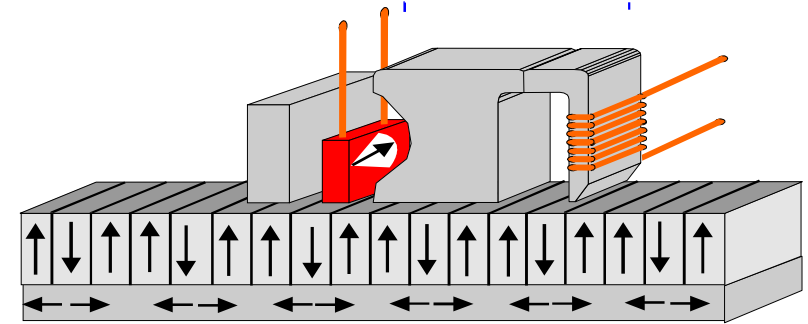
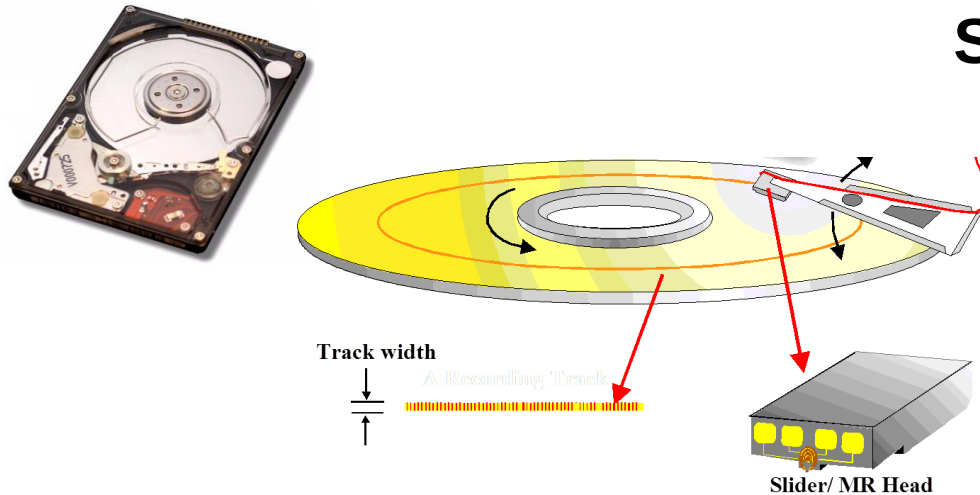


Appl. Phys. Lett. **102**, 052405 (2013)

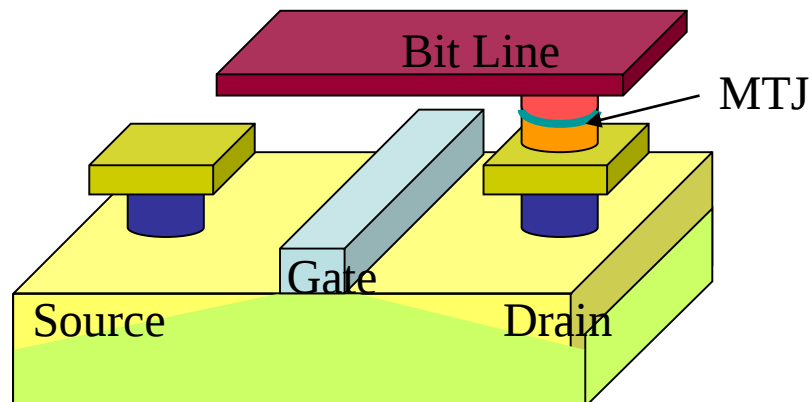


Magnetic Information technologies

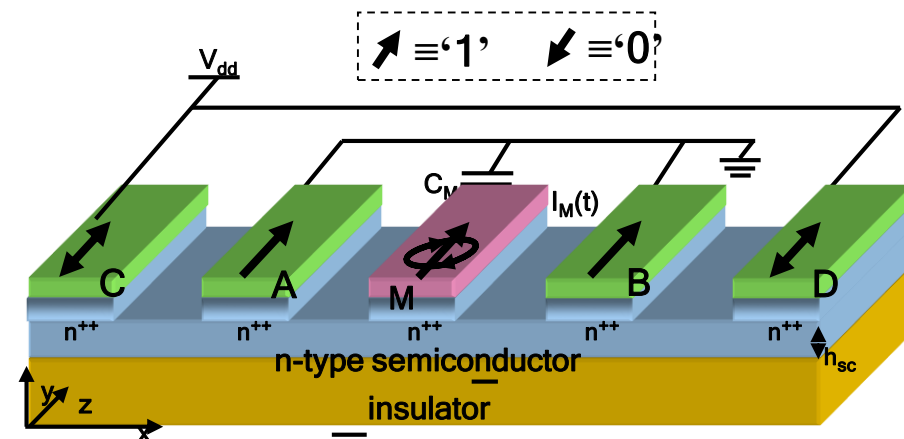
Storage – Hard Disk Drive



Memory – MRAM



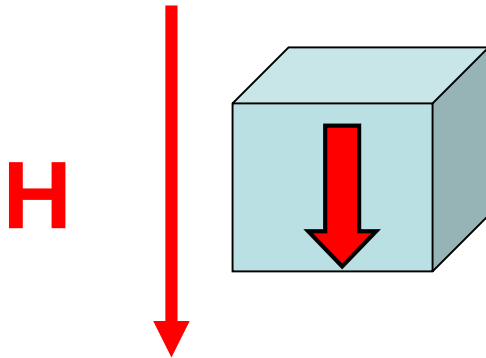
Processing



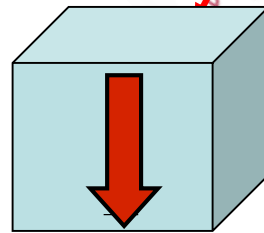
H. Dery, P. Dalal, L. Cywinski, L. J. Sham

Magnetic reversal

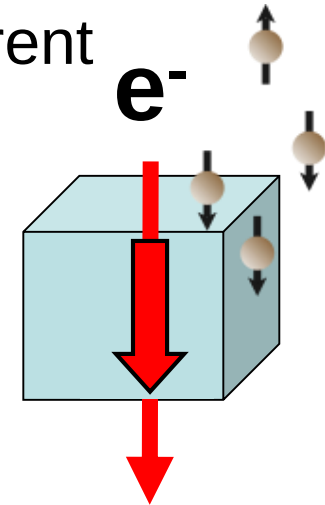
Field



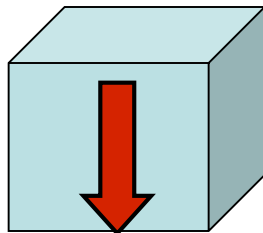
Light



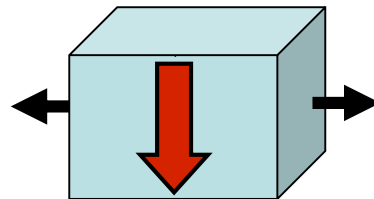
Current



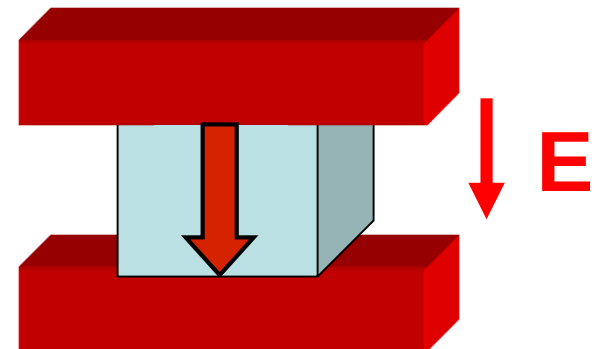
Heat



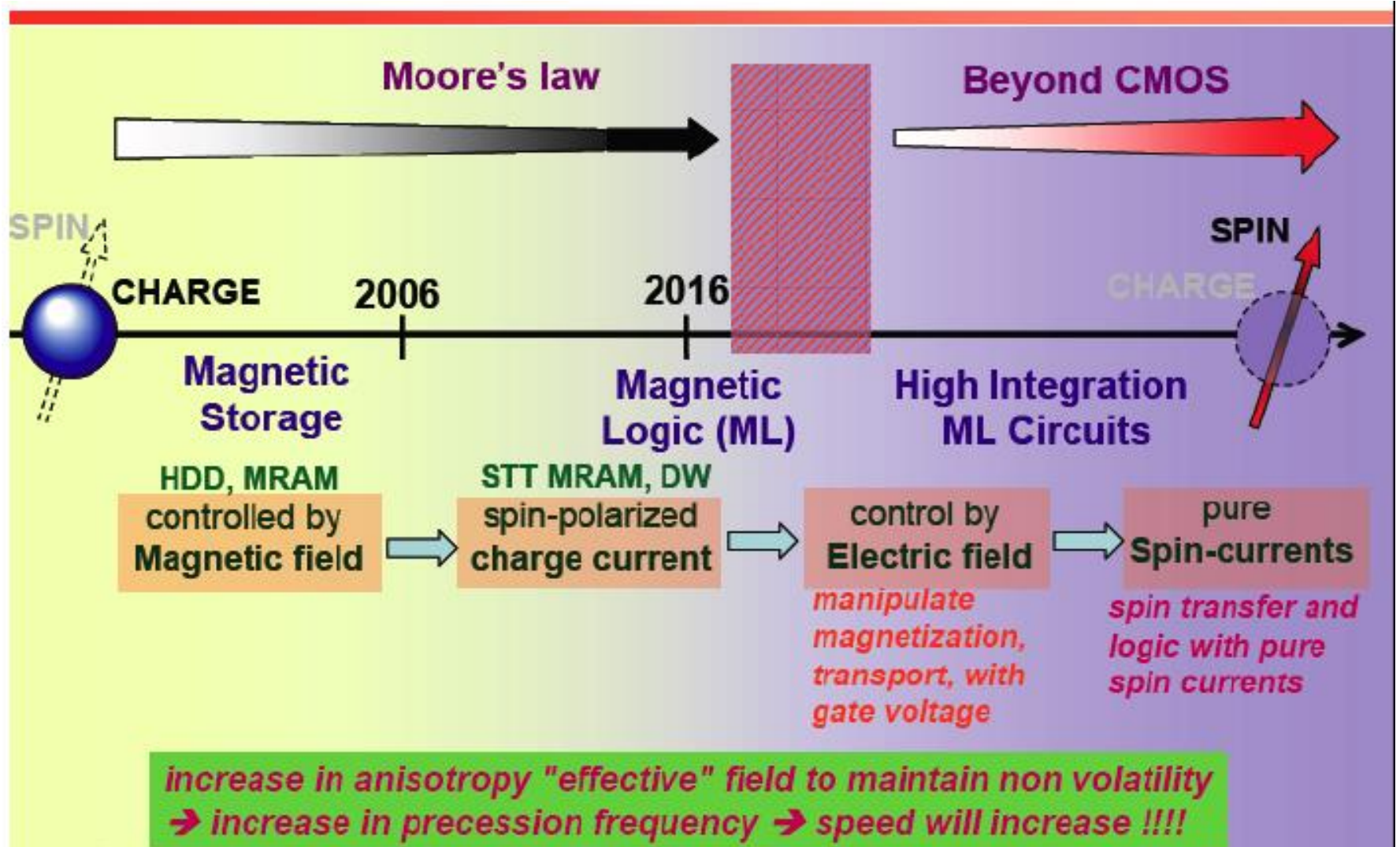
Strain



Electric Field



Claude Chappert's roadmap



Acknowledgements

Thank you and the organizers

M. Gottwald, C. H. Lambert, V. Uhler, J. Kan, Y. Fainman, V. Lomakin
University of California San Diego, CA, USA

S. Alebrand, D. Steil, M. Cinchetti, M. Aeschlimann
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D. Lacour, M. Hehn, S. Mangin
Institut Jean Lamour UMR CNRS 7198– Université de Lorraine, -Nancy, France

D. Ravelosona, *Institut d'Electronique Fondamentale , Orsay, France*

J.A. Katine, *HGST, A Western Digital Company*

D. Bedau, H. Liu, and A. Kent, *New York University*

K. Lee and S. Kang, *Qualcomm Inc.*

